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(54) **LIQUID CRYSTAL DISPLAY**

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(57) **ABSTRACT**

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**Related U.S. Application Data**

(63) Continuation of application No. 09/562,908, filed on May 2, 2000, which is a continuation of application No. 08/885,182, filed on Jun. 30, 1997, now Pat. No. 6,104,040.

A semiconductor element suitable for use in the display region of a liquid crystal display or for use in the drive circuit region for driving the display region is comprised of first, second, third and fourth electrodes; a pair of first conductivity type semiconductor layers separated from each other and connected to the second and the third electrodes, respectively; an intrinsic semiconductor layer connected to the pair of the first conductivity type semiconductor layers; and a second conductivity type semiconductor layer formed on the intrinsic semiconductor layer, wherein an insulating film is interposed between the first electrode and the intrinsic semiconductor layer, and the fourth electrode is formed on the second conductivity type semiconductor layer formed on the intrinsic semiconductor layer.

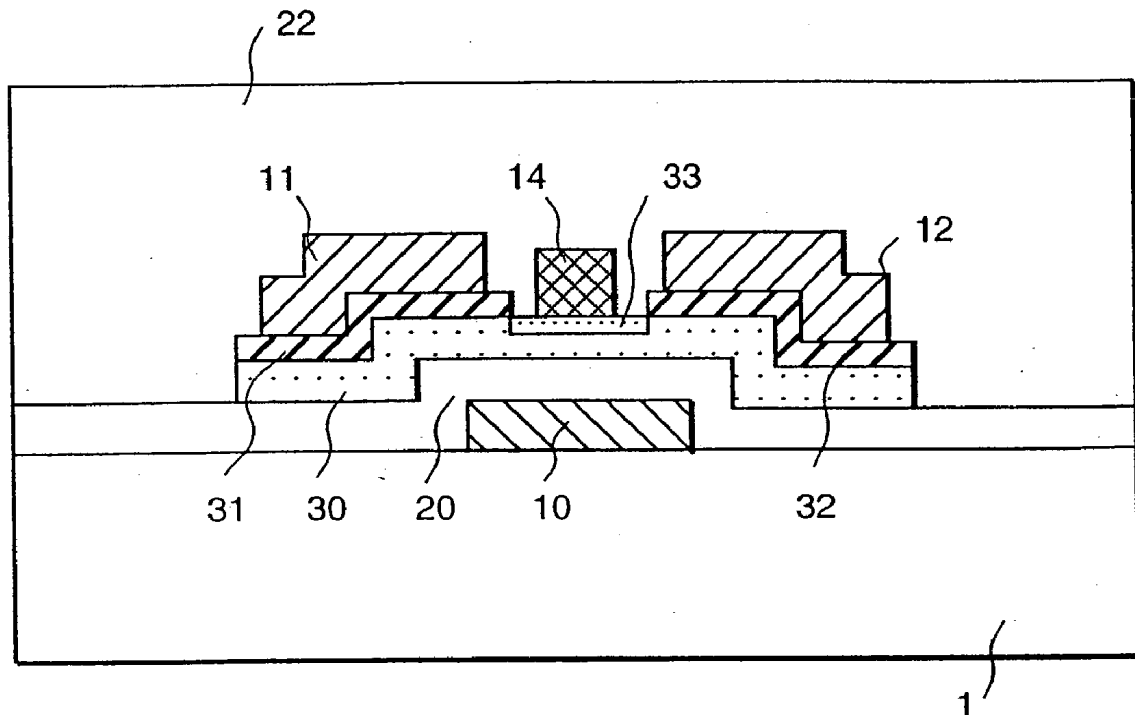


FIG. 1

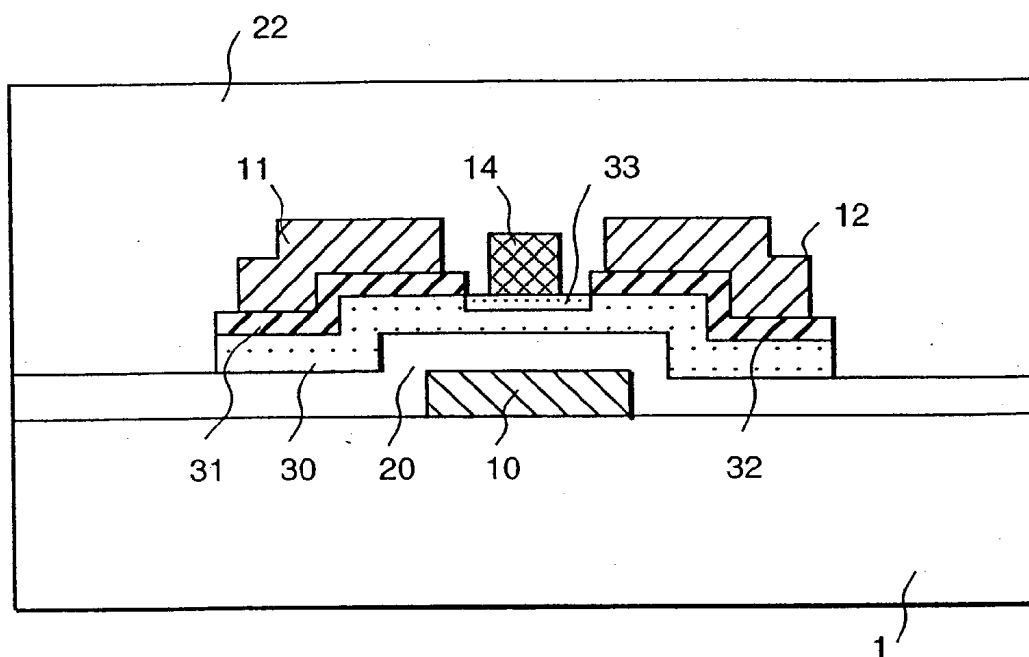
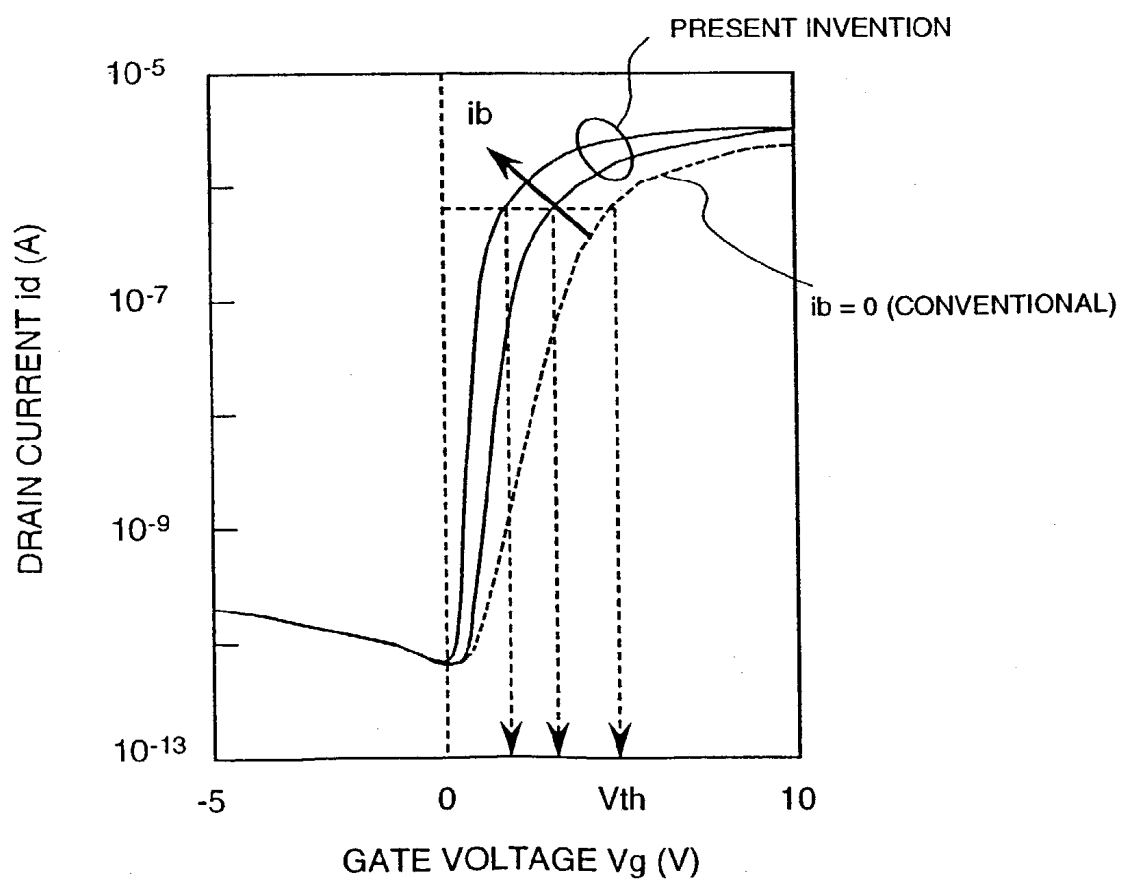
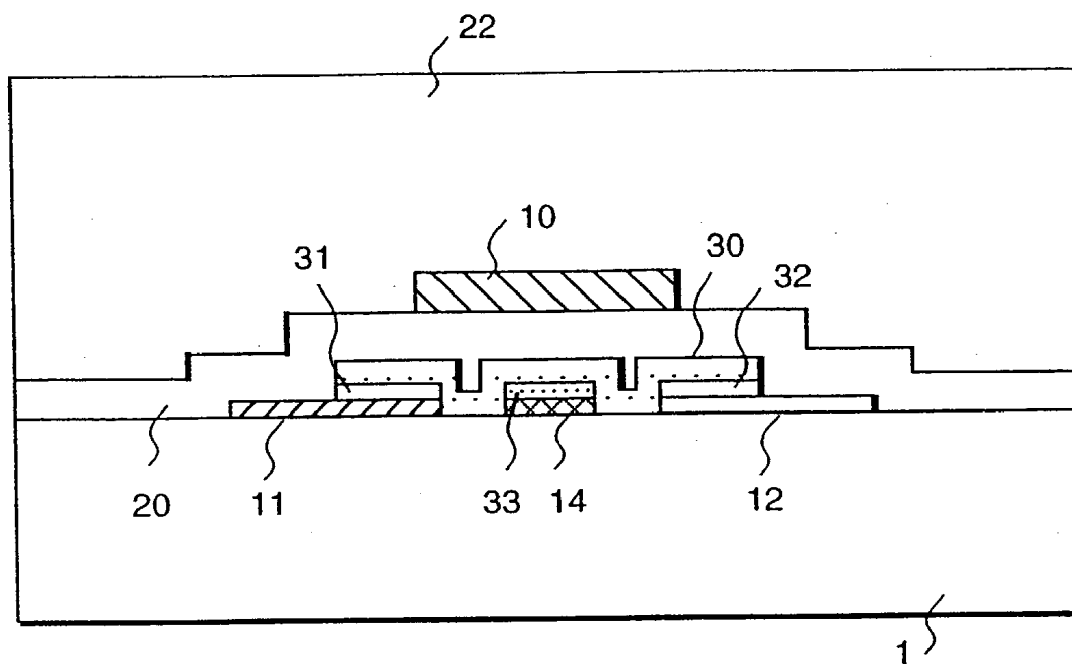


FIG. 4





**FIG. 5**



**FIG. 6**

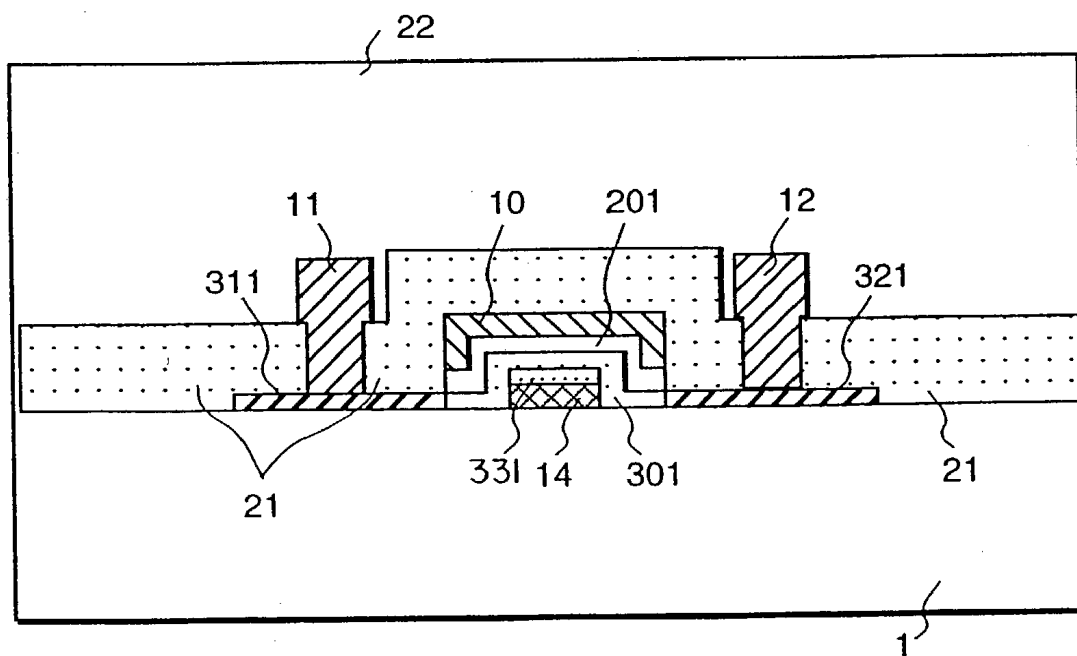


FIG. 7

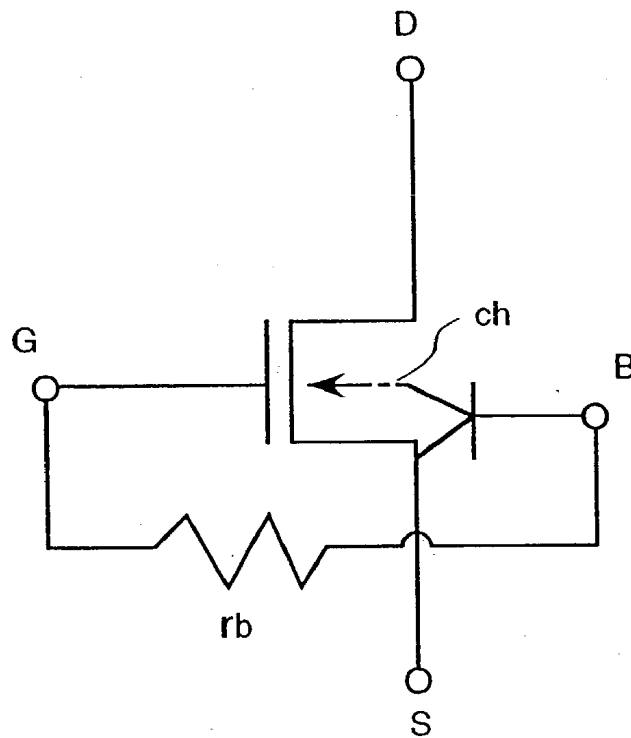


FIG. 8

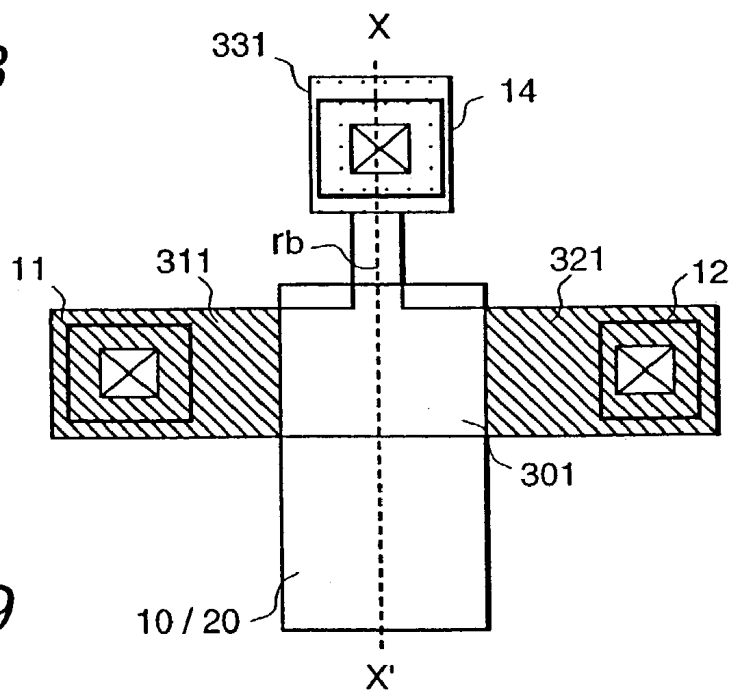
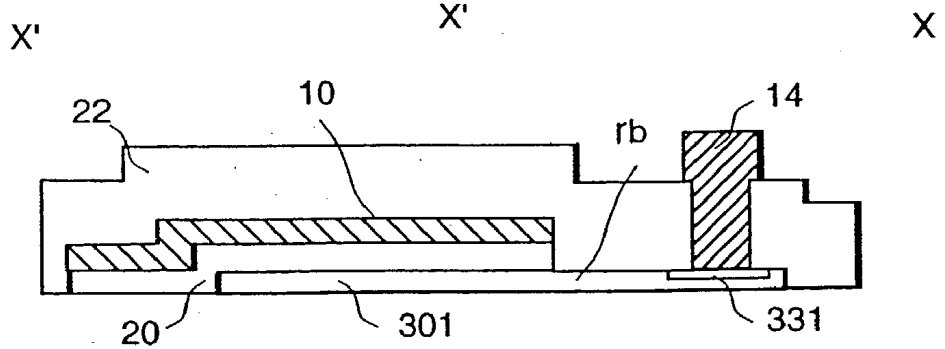
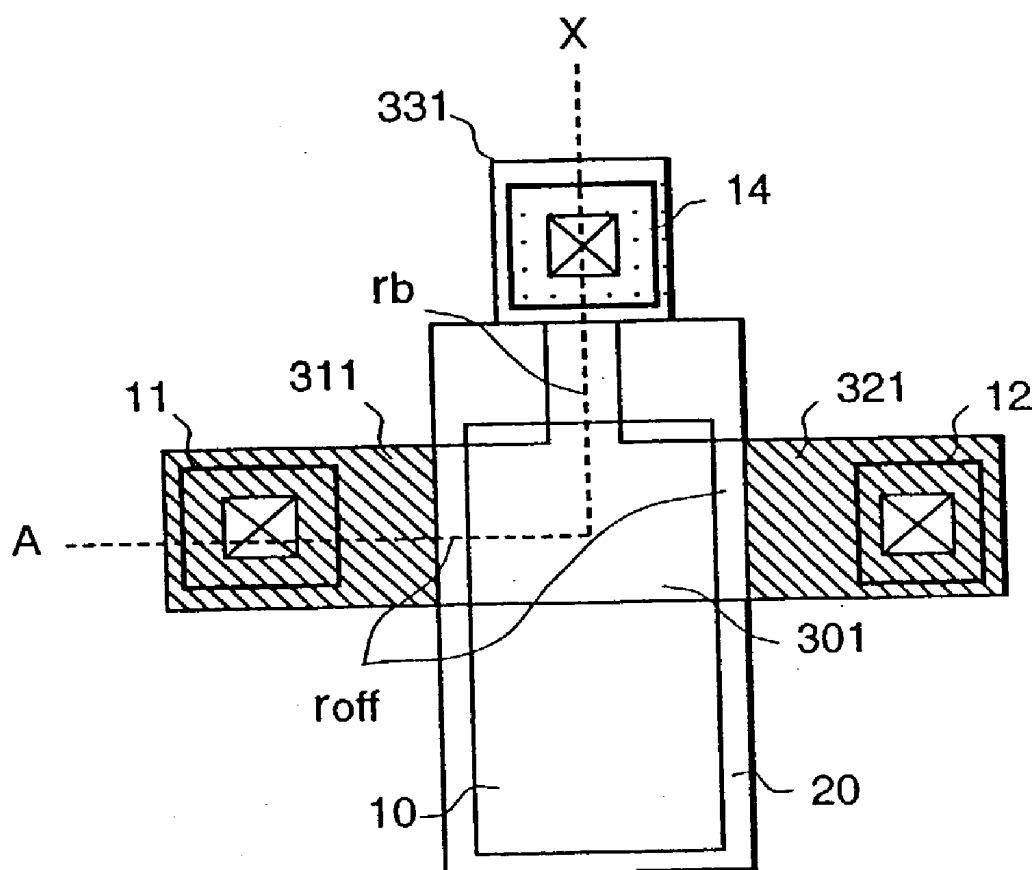


FIG. 9



**FIG. 10**



**FIG. 11**

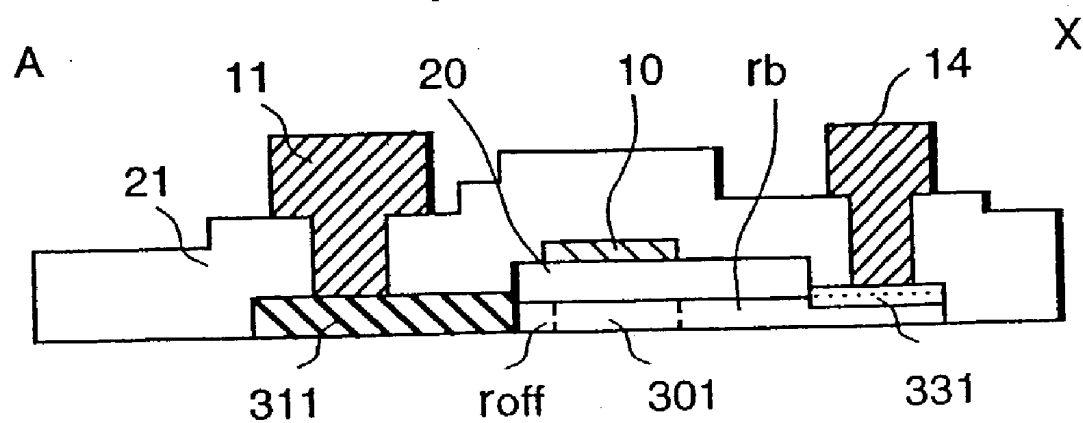


FIG. 12

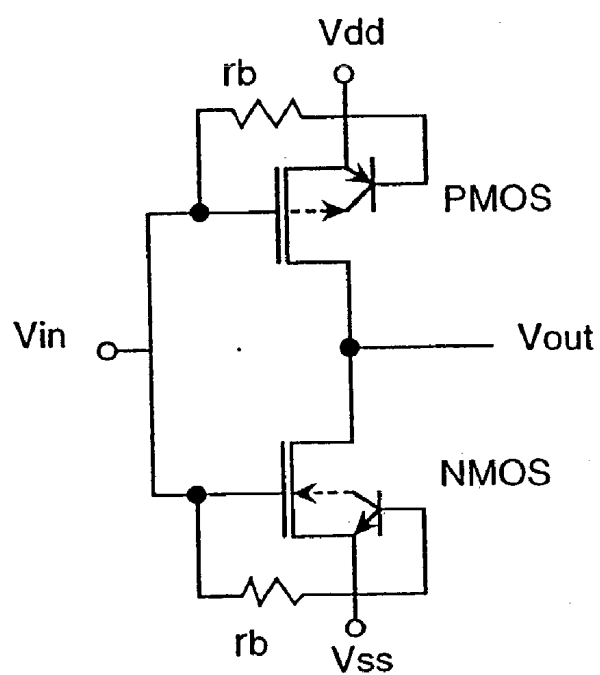


FIG. 13

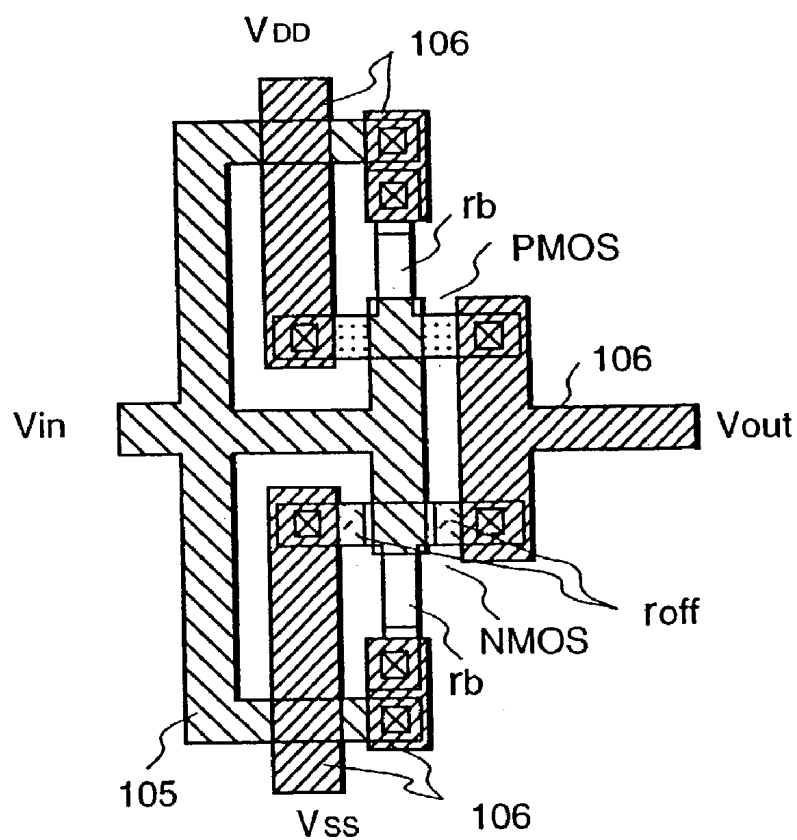


FIG. 14

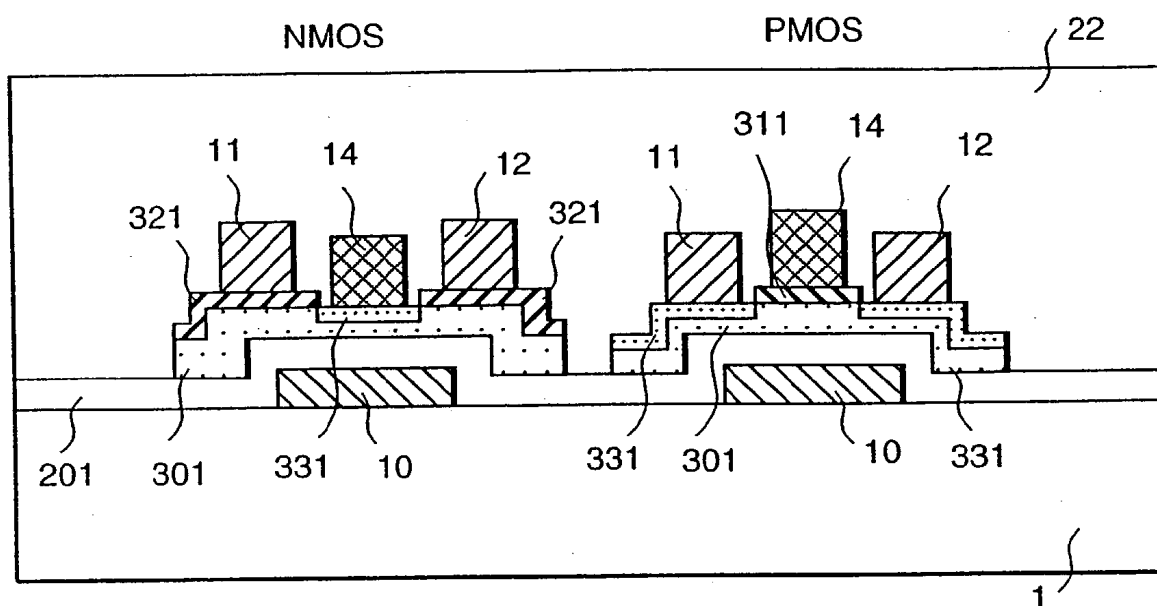


FIG. 15

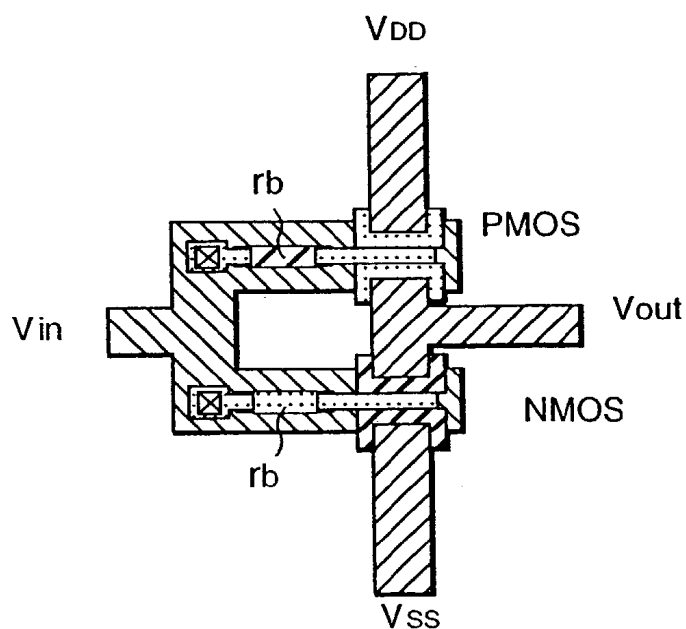


FIG. 16

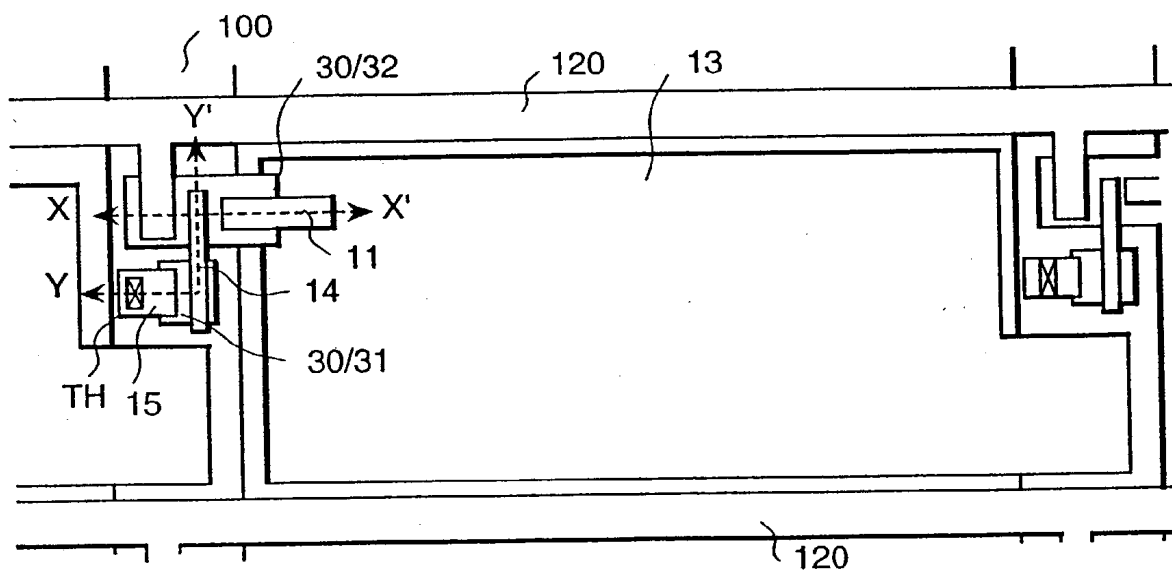


FIG. 17

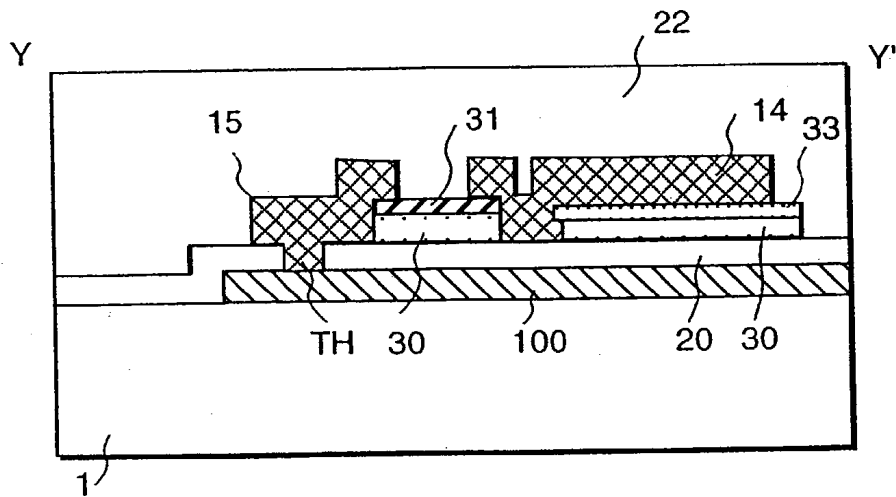


FIG. 18

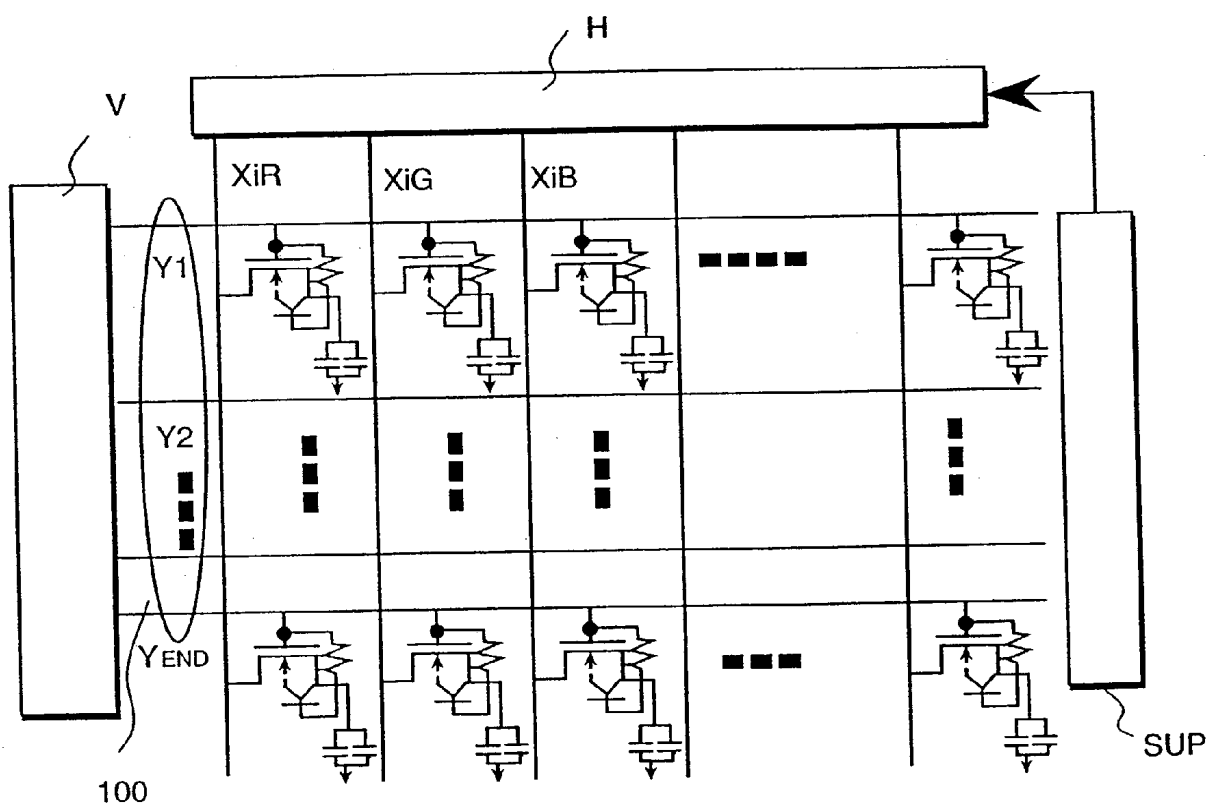


FIG. 19A

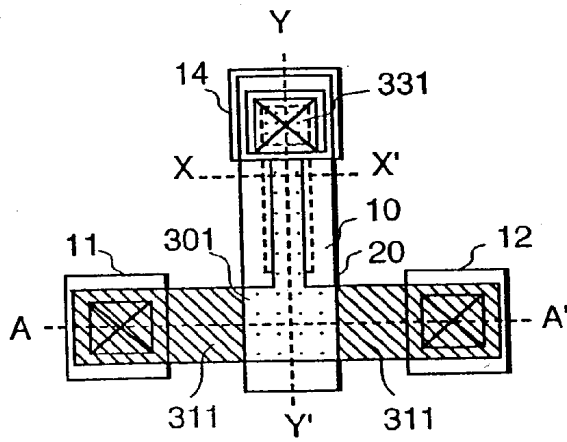


FIG. 19B

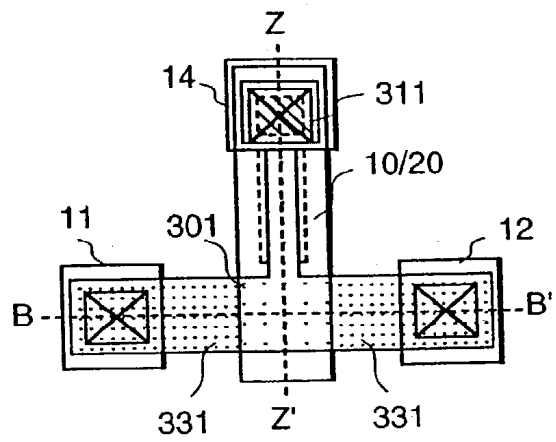


FIG. 19C

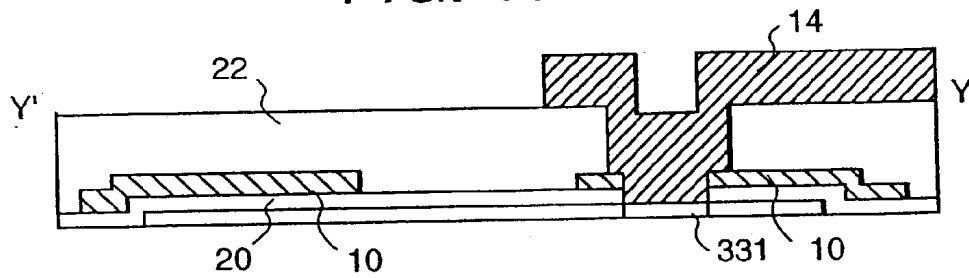


FIG. 19D

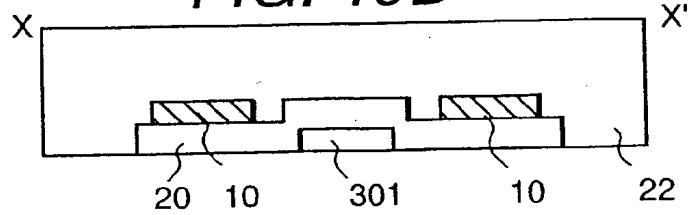


FIG. 20A

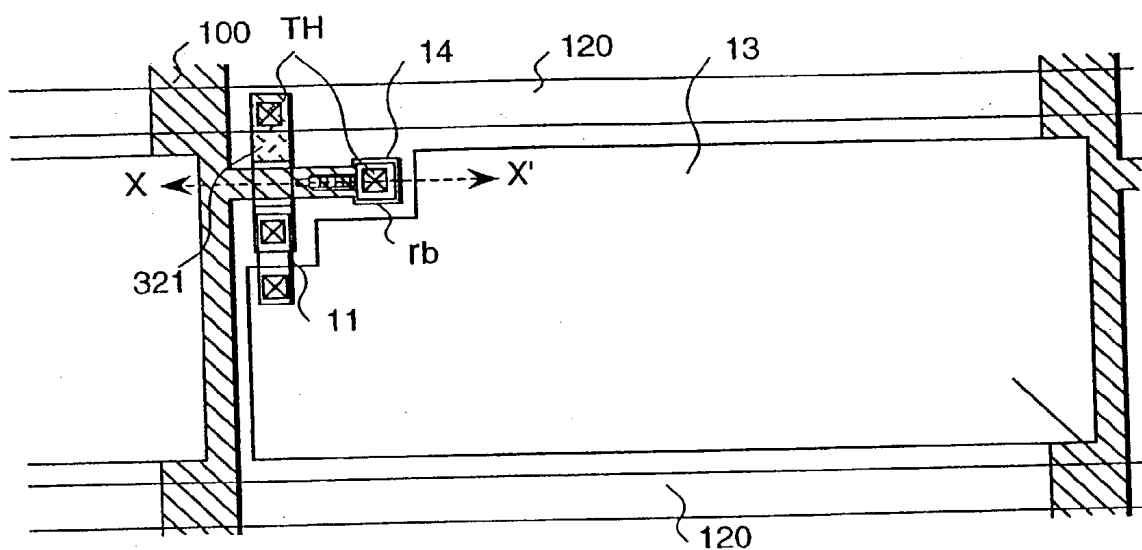


FIG. 20B

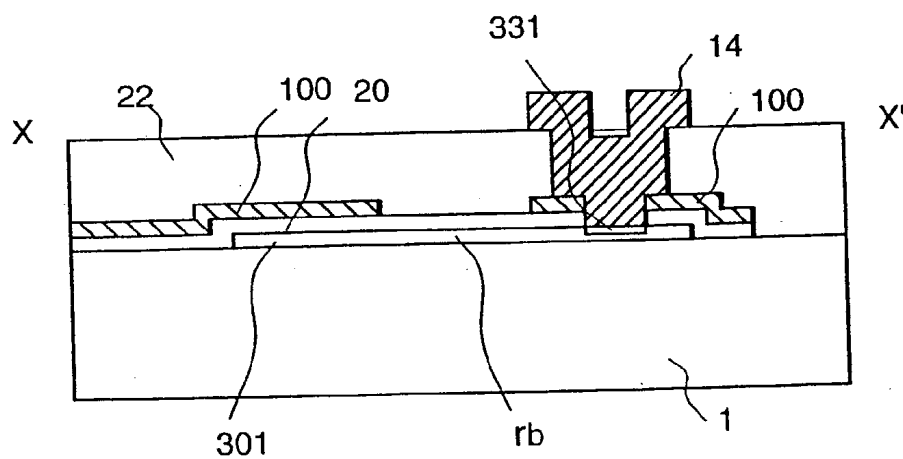


FIG. 21

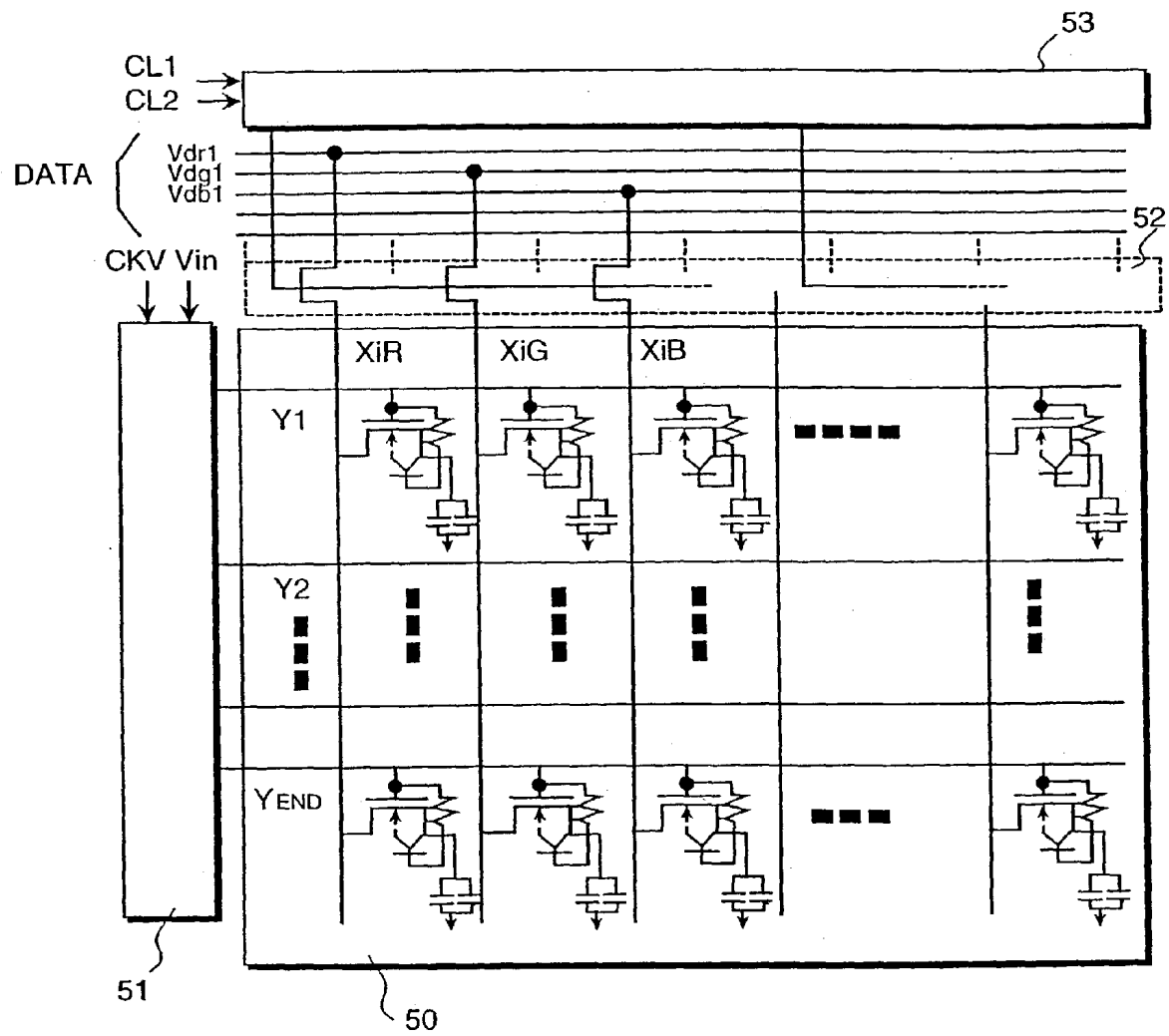


FIG. 22

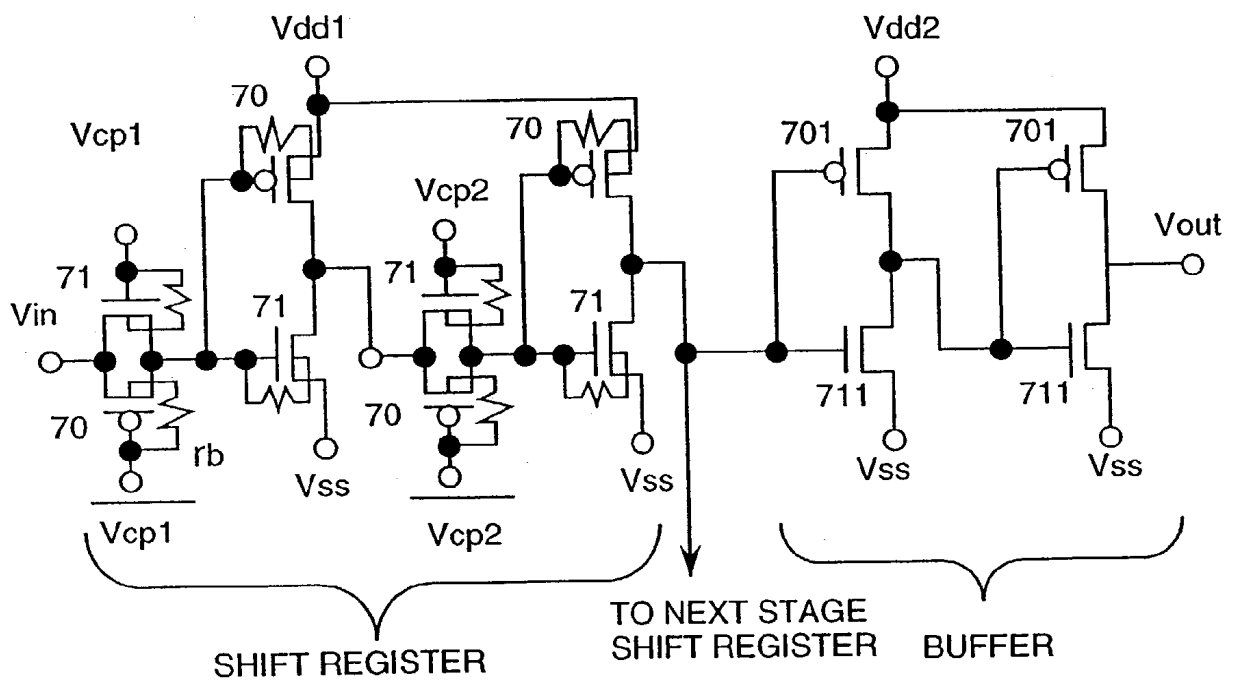


FIG. 23A

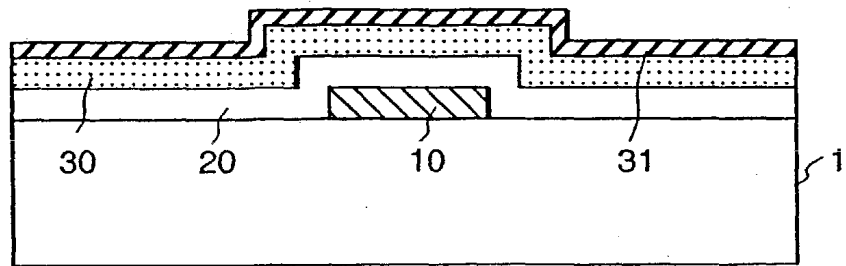


FIG. 23B

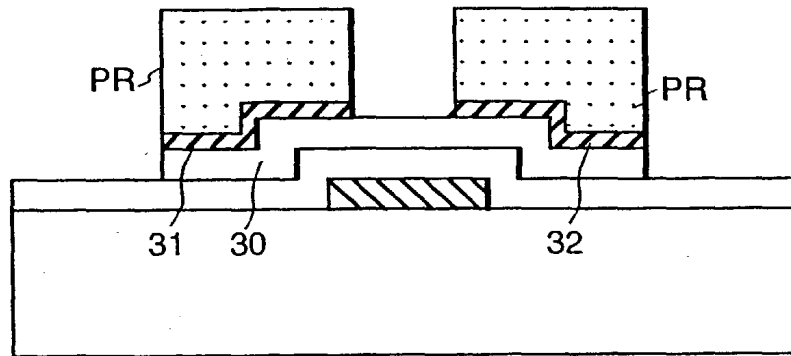


FIG. 23C

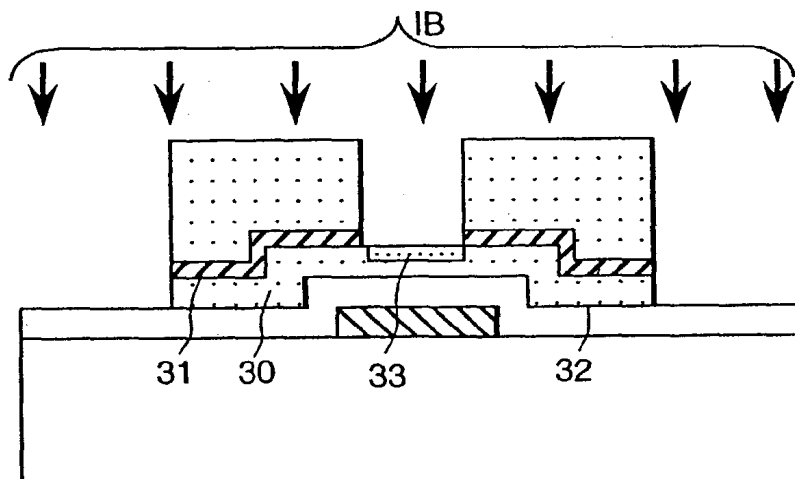


FIG. 23D

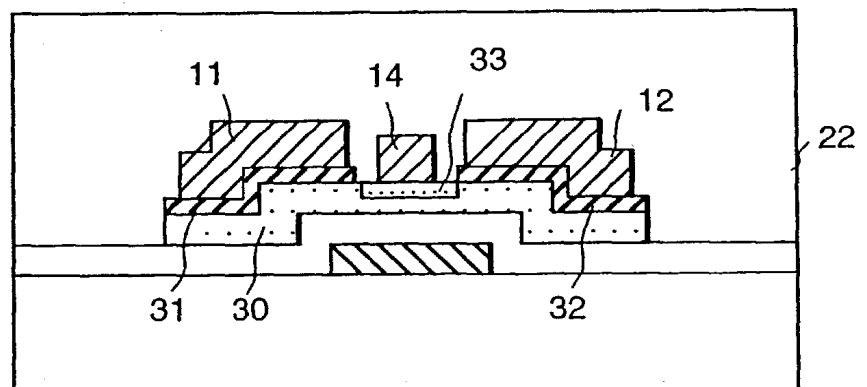


FIG. 24A

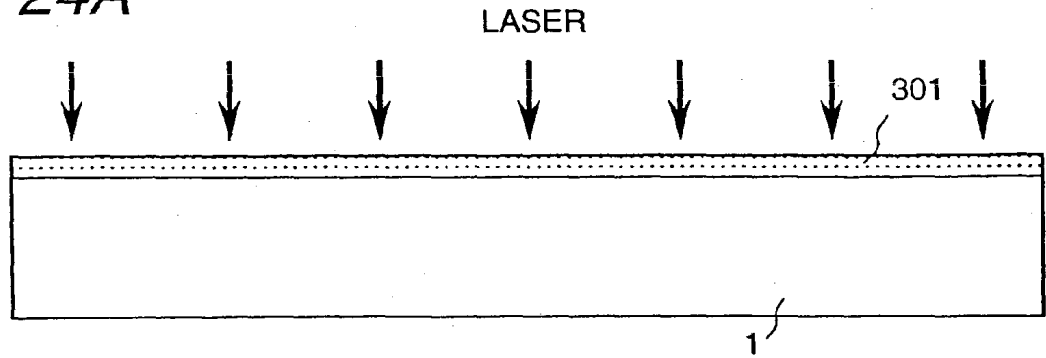


FIG. 24B

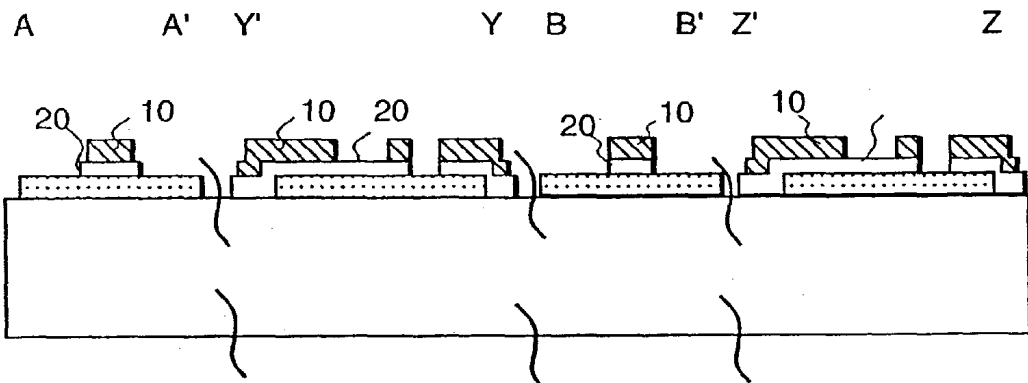


FIG. 24C

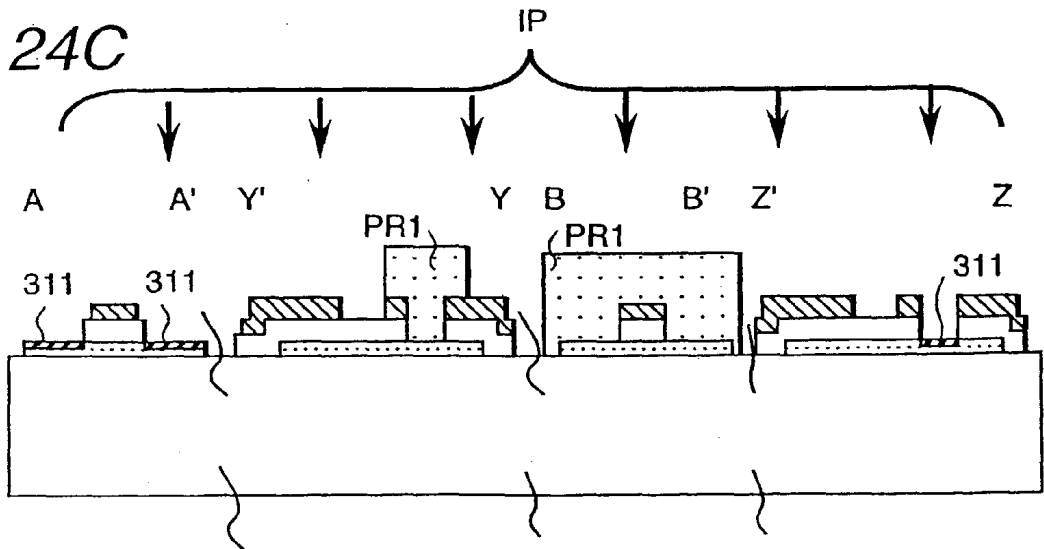


FIG. 24D

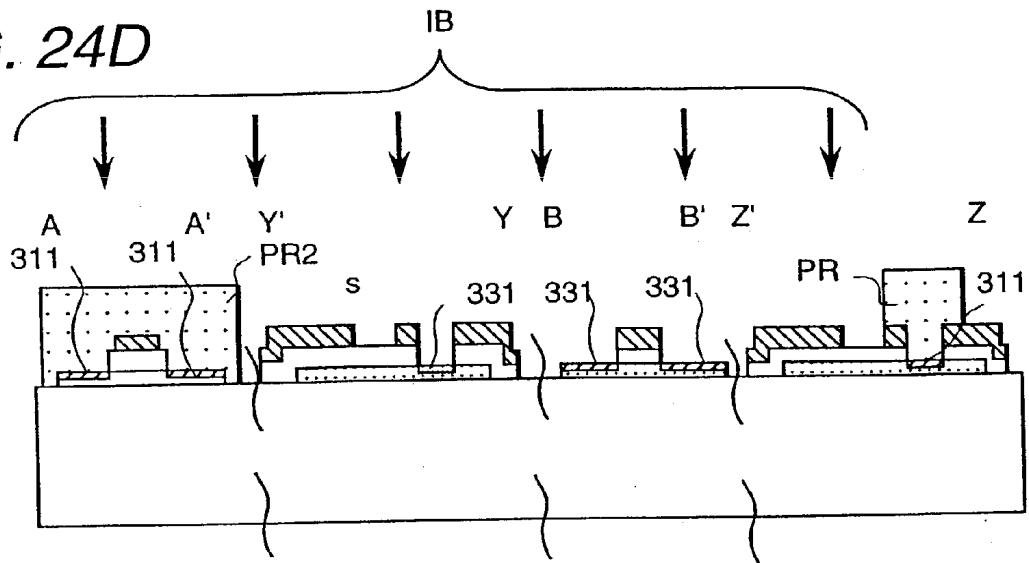


FIG. 24E

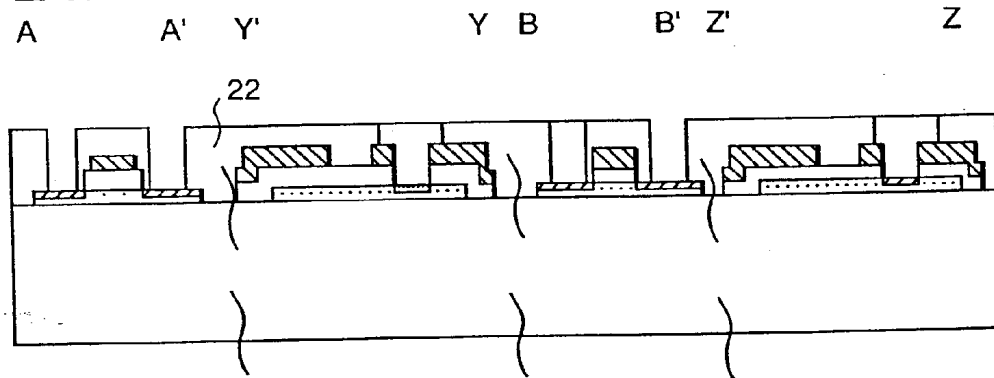


FIG. 24F

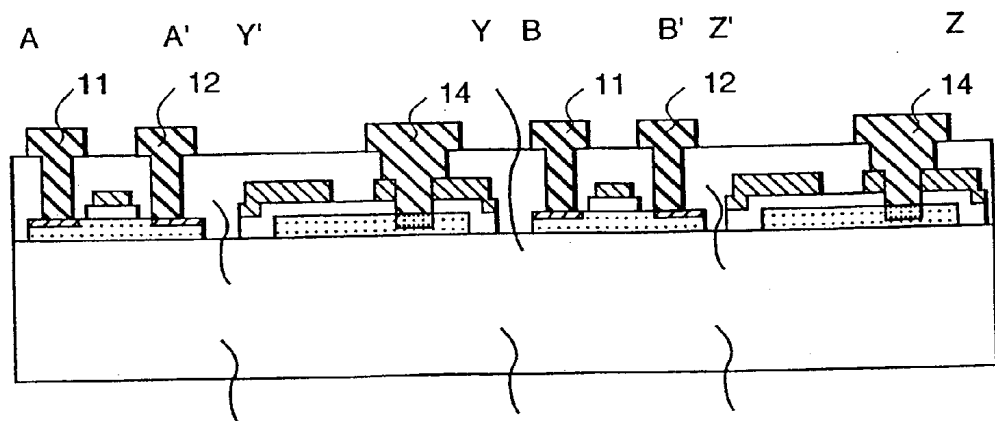


FIG. 25A

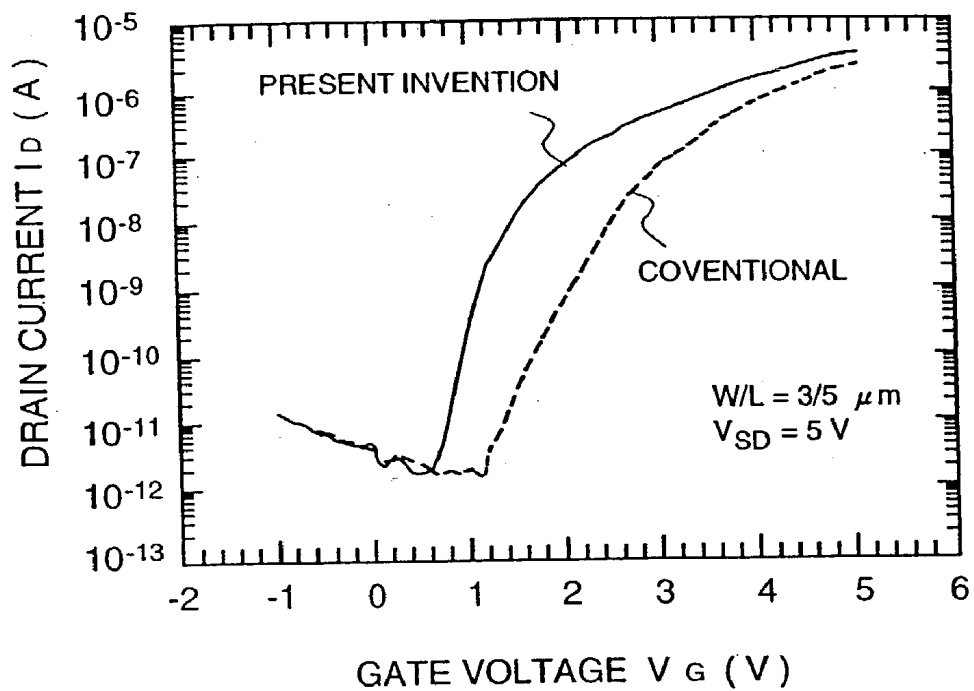


FIG. 25B

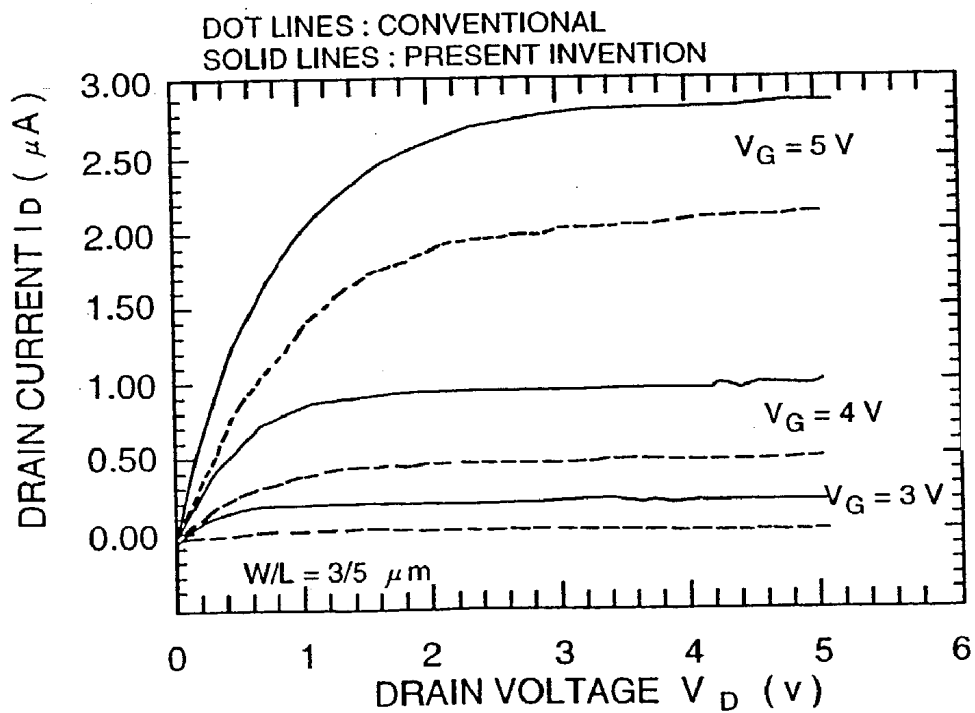


FIG. 26

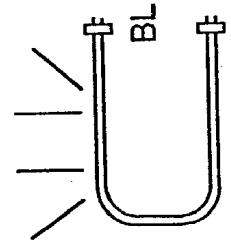
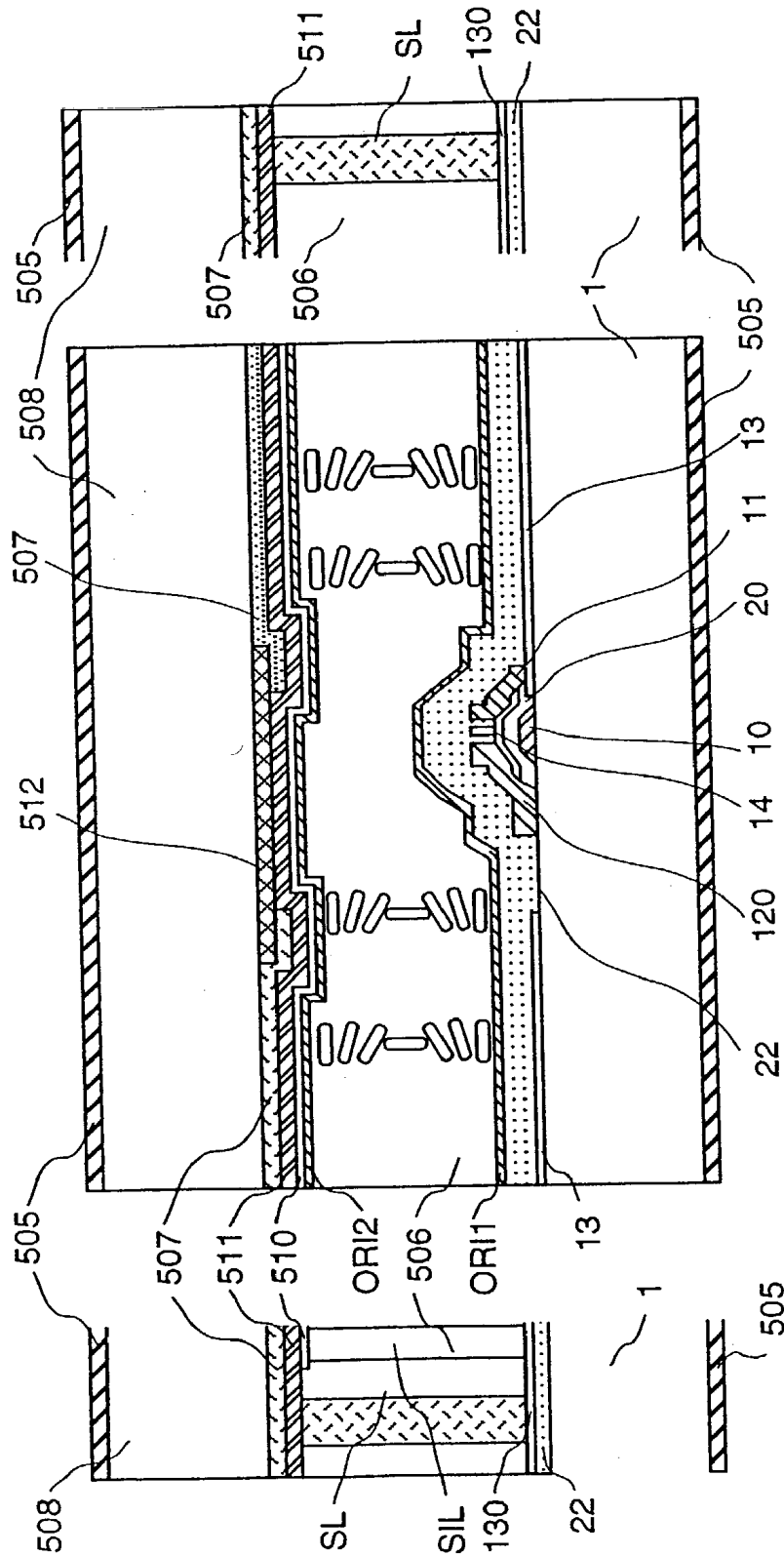
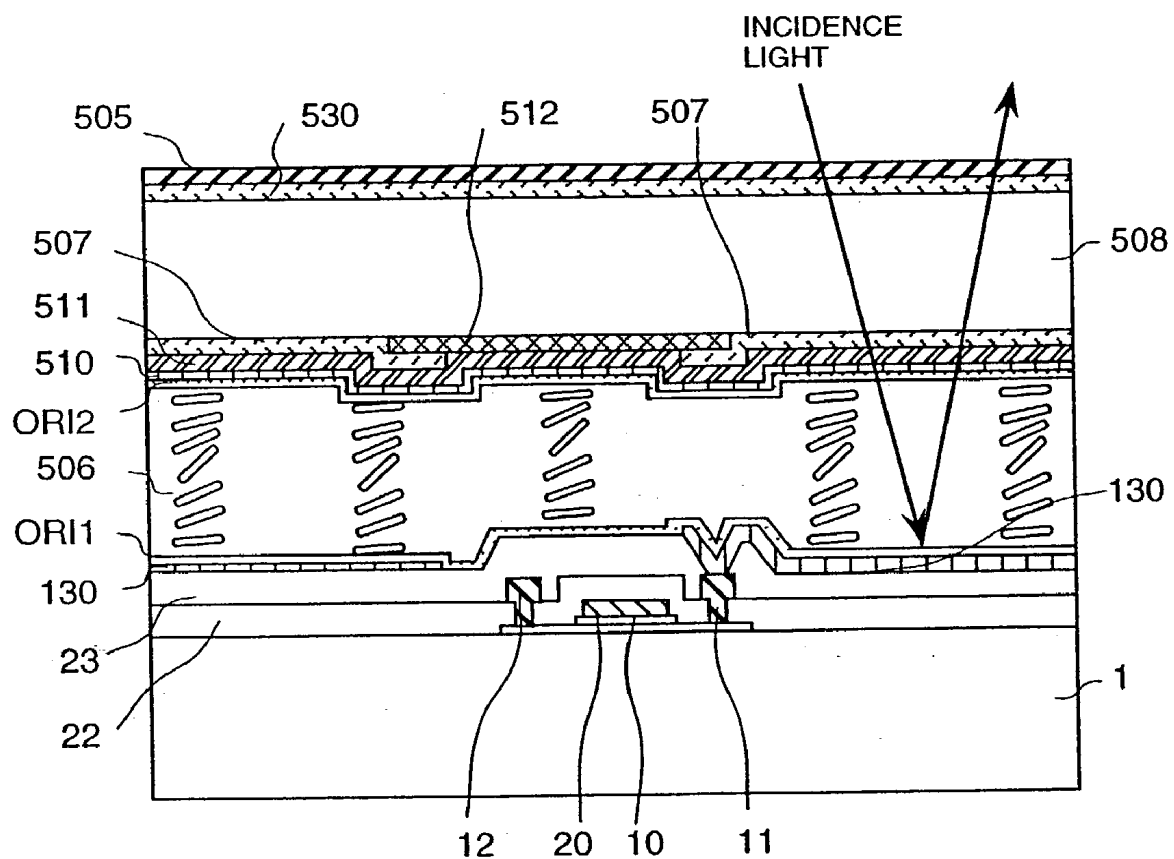


FIG. 27



## LIQUID CRYSTAL DISPLAY

### BACKGROUND OF THE INVENTION

[0001] The present invention relates to a semiconductor element and a liquid crystal display, and in particular, it relates to a semiconductor element, suitable for use as a thin film semiconductor element, and an active matrix addressing type liquid crystal display using the same.

[0002] As display devices for displaying image information and characters for use in the field of office automation equipment and the like, active matrix addressing liquid crystal displays using thin film transistors (hereinafter referred to as TFT) have been known. For this type of conventional liquid crystal display, further improvements in resolution and high quality of display, as well as cost reduction in manufacture, are necessary. In order to solve these problems, it is most important to improve the performance of the thin film transistor, which is a key device to the active matrix addressing liquid crystal display. In this regard, in the Conference Record of International Display Research Conference 1985, page 9, a concept of forming advanced high performance TFTs on a glass substrate was proposed, in which peripheral drive circuits for driving a TFT active matrix are fabricated using TFTs and are integrated with its display unit on the same substrate so as to reduce the cost of manufacture. With provision of advanced high performance peripheral drive circuits integrated on the glass substrate, since other circuits to be mounted externally and their mounting process can be simplified, a substantial reduction in the packaging cost can be expected. However, in order to provide these high performance circuits, development of a more improved, sophisticated high performance TFT is required. In particular, TFTs, which are formed on polycrystalline silicon (hereinafter referred to as poly-Si) and appear to be the most promising TFTs suitable for use in display equipment having integrated peripheral drive circuits, have further technical problems yet to be solved, which problems include the need for improvement of the carrier mobility and a lowering of the threshold voltage  $V_{th}$ .

[0003] A method of operation at a lower voltage by lowering the threshold voltage  $V_{th}$  of the transistors formed on an insulator has been proposed, as described in the Technical Digest of International Electron Device Meeting 1994, pages 809-812, in which a so-called dynamic threshold voltage MOSFET (hereinafter referred to as DTMOS) which has a fourth contact, separate from the source and drain, on a semiconductor film acting as a bipolar active layer, and is in contact with the gate electrode, is proposed as a submicron silicon-on-insulator (SOI) device.

[0004] In the technique described in the above-mentioned publication, the threshold voltage of the transistors is substantially reduced further to lower the operating voltage of the circuits thereof, thereby lowering the power supply voltage, and thus minimizing the power consumption in the drive circuits. This feature of decreased power consumption achieved by this drive circuit is desirable for use as a drive circuit and device for a liquid crystal display as well. It should be noted, however, that the above-mentioned publication is directed to the provision of logic devices or memory devices that can be operated at a low voltage and a high speed, and so they cannot be applied, as they are, to the drive devices for driving a liquid crystal display.

[0005] Namely, the semiconductor device, as described in the aforementioned publication at pages 809-812, is designed to operate effectively with a gate voltage at 0.6 V or less, and so this semiconductor device cannot be applied as it is to a liquid crystal display in which a lower limit of the gate drive voltage is determined by the liquid crystal drive voltage. More particularly, at least  $\pm 3$  V in peak amplitude is required for driving normal liquid crystal materials, thereby a higher voltage than this minimum peak voltage is required as the gate voltage for driving pixel drive transistors in a liquid crystal device. Thus, the semiconductor device described above, which operates at the gate voltage less than 1 V, cannot be applied to a liquid crystal display.

### SUMMARY OF THE INVENTION

[0006] An object of the invention is to provide an active matrix address type liquid crystal display in which the power consumption can be substantially reduced.

[0007] Another object of the invention is to provide a small power consumption liquid crystal display having a built-in drive circuit.

[0008] Still another object of the invention is to provide a drive circuit for use in a small power consumption liquid crystal display.

[0009] According to the invention, a semiconductor element for use as a switching element to be formed in a display area of the liquid crystal display or for use as a drive element to be formed in the area of a drive circuit for driving the display area is comprised of a first electrode, a second electrode, a third electrode and a fourth electrode; a pair of first conductivity type semiconductor layers separate from each other and connected to the second and the third electrodes, respectively; an intrinsic semiconductor layer connected to the pair of first conductivity type semiconductor layers; and a second conductivity type semiconductor layer formed on the intrinsic semiconductor layer; wherein an insulating film is interposed between the first electrode and the intrinsic semiconductor layer; and the fourth electrode is formed on the second conductivity type semiconductor layer which is formed on the intrinsic semiconductor layer.

[0010] Preferably, the pair of first conductivity type semiconductor layers and the second conductivity type semiconductor layer are separated from each other by the intrinsic semiconductor layer. Further, according to another aspect of the invention, the intrinsic semiconductor layer extends in lateral directions beyond the insulating layer at least towards the pair of the first conductivity type semiconductor layers on the substrate.

[0011] The first electrode and the fourth electrode are electrically connected via a resistance advantageously for wiring the liquid crystal display.

[0012] The intrinsic semiconductor layer, the first conductivity type semiconductor layers and the second conductivity type semiconductor layer are preferably formed of a thin film semiconductor made either of silicon, silicon germanium or silicon carbide. Further, they may be made of polycrystalline silicon films as well. In particular, it is preferable to use polycrystalline silicon films in a drive circuit built-in type liquid crystal display.

[0013] The semiconductor element of the invention can be designed to have a structure either of a planar type, an inverted staggered type or a positive staggered type. In the case of the inverted staggered type, a first electrode is formed on one of a pair of substrates, an insulating layer is formed on the first electrode, and an intrinsic semiconductor layer is formed on this insulating layer, then a pair of first conductivity type semiconductor layers are formed on the intrinsic semiconductor layer. Further, in the case of the planar type, the second, the third and the fourth electrodes are formed on one of the pair of substrates.

[0014] In the cases of both the positive staggered and the inverted staggered types, it is also possible for either one of the pair of the first conductivity type semiconductor layers or the second conductivity be formed by self-alignment utilizing a counterpart's pattern as its own masking pattern.

[0015] The semiconductor element of the invention can be used as complementary N-type and P-type semiconductor elements which can be formed in the drive circuit region in the liquid crystal display. More particularly, since a vertical scanning circuit and a picture signal drive circuit are provided in the drive circuit region, the complementary semiconductor element of the invention can be applied to a shift register within these circuits. More specifically, when the semiconductor element of the invention is used in the drive circuit region in a peripheral circuit built-in type liquid crystal display, the power consumption thereof can be reduced effectively and substantially.

[0016] According to the invention, an intrinsic semiconductor layer is formed as an i semiconductor layer between the first, the second and the third electrodes. Into this intrinsic semiconductor layer, a current carrier is injected which has a different polarity from the polarity of a current carrier in the impurity semiconductor layers of the first conductivity type which are connected to the second and the third electrodes respectively. According to this arrangement, when the impurity semiconductor layers connected to the second and the third electrodes, respectively, are formed of an n-type semiconductor layer, there is formed a p-i-n junction between a current carrier injection layer or the fourth electrode and the second electrode.

[0017] Further, when a voltage applied across the current carrier injection layer, i.e., the fourth electrode and the second electrode, is  $V_b$ , the voltage  $V_b$  is divided between an i-n junction and the i layer of the p-i-n junction, thereby preventing an excess current (base current) from flowing. Thereby, operation at a low power can be ensured until the gate voltage (to be applied to the first electrode) increases substantially. Namely, if a P-type or N-type semiconductor layer is used in place of the intrinsic semiconductor of the invention, a full voltage of  $V_b$  is applied to the source junction, and if  $V_b$  exceeds a built-in voltage (approximately 0.6 V) of the source junction, an excess current is caused to flow, thereby rapidly increasing the power consumption. In contrast, if an active semiconductor layer is comprised of an intrinsic semiconductor, excess base current will not flow until a substantially higher gate voltage is applied, thereby ensuring operation at a low power. In this case, due to adoption of the p-i-n junction, the degree of drop in the threshold voltage becomes mild, but it is still substantial compared to the conventional elements. Due to this drop in the threshold voltage, it becomes possible to operate the

liquid crystal driving elements and associated peripheral circuits at lower voltages, thereby substantially reducing power consumption in active matrix type displays. BRIEF

#### DESCRIPTION OF THE DRAWINGS

[0018] These and other objects, features and advantages of the present invention will be understood more clearly from the following detailed description when taken with reference to the accompanying drawings, wherein:

[0019] **FIG. 1** is a cross-sectional view of a semiconductor element according to one embodiment of the invention;

[0020] **FIG. 2** is a schematic diagram in cross-section of the semiconductor element of **FIG. 1** indicative of the principles of operation thereof;

[0021] **FIG. 3** is a schematic diagram of energy bands indicative of the principles of operation of the semiconductor element of **FIG. 1**;

[0022] **FIG. 4** is a diagram indicative of transfer characteristics of the semiconductor element of **FIG. 1**;

[0023] **FIG. 5** is a cross-section of a semiconductor element according to a second embodiment of the invention;

[0024] **FIG. 6** is a cross-section of a semiconductor element according to a third embodiment of the invention;

[0025] **FIG. 7** is an equivalent circuit diagram of a semiconductor element according to a fourth embodiment of the invention;

[0026] **FIG. 8** is a plan view of a semiconductor element according to a fifth embodiment of the invention;

[0027] **FIG. 9** is a cross-section of a TFT taken along line X-X' in **FIG. 8**;

[0028] **FIG. 10** is a plan view of a semiconductor element according to a sixth embodiment of the invention;

[0029] **FIG. 11** is a cross-section of a TFT taken along line X-A in **FIG. 10**;

[0030] **FIG. 12** is a circuit diagram of a complementary type inverter according to a seventh embodiment of the invention;

[0031] **FIG. 13** is a plan view of the complementary type inverter of **FIG. 12**;

[0032] **FIG. 14** is a cross-section of a complementary type inverter according to an eighth embodiment of the invention;

[0033] **FIG. 15** is a plan view of the complementary type inverter of **FIG. 14**, which is a planar type semiconductor element of the invention;

[0034] **FIG. 16** is a plan view of a unit picture element in a liquid crystal display according to a ninth embodiment of the invention;

[0035] **FIG. 17** is a cross-section of the liquid crystal display taken along line Y-Y' in **FIG. 16**;

[0036] **FIG. 18** is an equivalent circuit indicative of a schematic configuration of the liquid crystal display;

[0037] **FIGS. 19A and 19B** are plan views and **FIGS. 19C and 19D** are cross-section views of a semiconductor element according to a tenth embodiment of the invention;

[0038] FIG. 20A is a plan view and FIG. 20B is a cross-section of a unit picture element of a liquid crystal display constructed using the semiconductor element of FIGS. 19A-19D;

[0039] FIG. 21 is an equivalent circuit of a drive circuit built-in type liquid crystal display constructed using the semiconductor element of FIGS. 19A-19D;

[0040] FIG. 22 is a schematic circuit diagram including a shift register and a buffer used in the drive circuit built-in type liquid crystal display of FIG. 21;

[0041] FIGS. 23A to 23D are cross-sectional views of a semiconductor element indicative of steps of a process of fabrication thereof according to an eleventh embodiment of the invention;

[0042] FIGS. 24A to 24F are cross-sectional views of a semiconductor element indicative of steps of a process of fabrication thereof according to a twelfth embodiment of the invention;

[0043] FIGS. 25A and 25B are diagrams indicative of current-voltage characteristics of the semiconductor element of FIGS. 19A-19D;

[0044] FIG. 26 is a cross-section of a liquid crystal cell of a liquid crystal display according to a thirteenth embodiment of the invention; and

[0045] FIG. 27 is a cross-section of a liquid crystal cell of a liquid crystal display according to a fourteenth embodiment of the invention.

#### DESCRIPTION OF THE PREFERRED EMBODIMENTS

[0046] Preferred embodiments of the invention will be described in detail with reference to the accompanying drawings.

[0047] First Embodiment:

[0048] With reference to FIG. 1, a first embodiment of the invention will be described in the following. FIG. 1 is a cross-sectional view of a semiconductor element according to the first embodiment, which has a gate electrode 10 as a first electrode made of chromium and formed on the surface of a glass substrate 1. Gate electrode 10 is overlaid by a gate insulating film 20 consisting of a SiN film. An intrinsic a-Si layer 30 is formed on gate insulating film 20. On the surface of the intrinsic a-Si layer 30, there are formed n-type a-Si layers 31, 32 which are doped with phosphor, and a p-type a-Si layer 33 which is doped with boron.

[0049] A p-type a-Si layer 33 is formed between a pair of n-type a-Si layers 31 and 32 on the intrinsic a-Si layer 30 by self-alignment using the pattern of n-type a-Si layers 31 and 32 as its own masking pattern. Use of the pattern of the n-type a-Si layers 31, 32 as its own mask pattern thereby to form the p-type a-Si layer 32 will enable forming both of the n-type a-Si layers 31, 32 and the p-type a-Si layer 33 by a single photolithographic process, thereby simplifying the fabrication process thereof and thus decreasing the production cost. Further, as the second and the third electrodes to be connected to the n-type a-Si layers 31 and 32, respectively, a source electrode 11 and a drain electrode 12 made of titanium are formed. Further, a base electrode 14 is formed in contact with the p-type a-Si layer 33 as a hole

injection electrode. Then, the entire portion of the element is overlaid by a passivation film 22 made of SiN film, thereby providing for an n-type field effect transistor according to the invention.

[0050] Namely, according to this embodiment of the invention, the majority carrier is an electron, and the minority carrier is a hole. By applying a positive voltage, which is positive relative to the source electrode 11, to the base electrode 14, which is in contact with the p-type a-Si layer 33, the minority carrier of holes is caused to be injected into the intrinsic silicon layer 30.

[0051] Now, with reference to FIGS. 2 and 3, the operation of the semiconductor element of FIG. 1 will be described specifically. In the n-type transistor, with reference to FIG. 2, a conduction state (ON-state) is realized by applying positive voltages  $V_g$  and  $V_d$ , which are positive relative to source electrode 11, which is at ground potential, to the gate electrode 10 and the drain electrode 12, respectively. At this time, a positive voltage  $V_b$  is applied to the fourth electrode 14 (hereinafter referred to as the base electrode) which is in contact with the p-type layer 33 formed on the intrinsic semiconductor layer. By application of the positive voltage  $V_b$ , an n-i-p junction, comprised of the n+layer 31 in contact with the source electrode 11, the intrinsic semiconductor layer 30 and the p-layer 33, is biased in the forward direction, thereby causing holes to be injected through the p-layer 33 into the intrinsic semiconductor layer. A flow of injected holes is depicted by  $\phi_h$ . Then, the injected holes drift toward the source electrode 11, but are blocked by a potential barrier at an n+/i junction formed between the n+layer 31 and the intrinsic semiconductor layer 30, thereby being accumulated in the vicinity of the n+/i junction. The accumulated holes in turn cause the potential barrier at the n+/i junction to be lowered. Thereby, a large amount of electrons are injected from the n+layer 31 into the intrinsic semiconductor layer 30 toward a channel formed at a boundary between the intrinsic-semiconductor layer 30 and the gate insulating film 20. A flow of injected electrons is depicted by  $\phi_e$ . As a result, a substantial increase in the majority carrier current (electrons) can be realized by the injection of a small amount of minority carrier current (holes) according to the invention.

[0052] The status of carrier flows across energy bands at the source junction along line X-X' of FIG. 2 is depicted in FIG. 3, where it is indicated that holes injected from the base electrode 14 are blocked by the potential barrier at the n+/i junction so as to be accumulated in the vicinity of the n+/i junction. Thereby, the potential energy in the intrinsic semiconductor layer 30 changes from its initial status prior to the accumulation of the injected holes, which is depicted by dotted lines, to a status as depicted by solid lines, thereby lowering the potential barrier against a mass of electrons present in the n+layer 31, thereby allowing the mass of electrons to be injected toward the channel ch as depicted by  $\phi_e$ .

[0053] On the other hand, in order to cut-off the transistor, a negative voltage is applied to gate 10 as well as to base electrode 14 such that the n-i-p junction is biased in the reverse direction. When the n-i-p junction is reversely biased, the injection of holes from the base electrode 14 is stopped, thereby interrupting the current.

[0054] According to the feature of this embodiment of the invention, the effect of current amplification in the transistor

is most significant in a subthreshold region in which electron current is restricted due to injection from the source electrode **11**, and thus the transfer characteristics therein change such that a current rise becomes steep in the subthreshold region **R** with an increasing base current  $i_b$  as indicated in **FIG. 4**, thereby advantageously allowing the threshold voltage  $V_{th}$  to decrease.

[0055] According to this feature of this embodiment of the invention as described above, since the intrinsic semiconductor layer **30** is used as its semiconductor layer, when a voltage  $V_b$  is applied between the base and the source, the voltage  $V_b$  is subdivided between the i-layer and the i/n junction of the p-i-n junction, thereby preventing an excess base current from flowing until a substantially higher voltage is applied across the base and the source, thereby ensuring operation at a higher gate voltage, for example, exceeding  $\pm 5V$  and at a reduced power consumption. Thereby, when a semiconductor device having a threshold voltage which can be lowered is utilized as a liquid crystal driving element or as a peripheral circuit device thereof, it becomes possible to lower the voltage to drive the liquid crystal display, thereby minimizing the power consumption in the active matrix addressing type display.

[0056] Second Embodiment:

[0057] **FIG. 5** is a cross-sectional view of a semiconductor device according to a second embodiment of the invention.

[0058] The semiconductor device according to the second embodiment of the invention has a structure of a positive stagger type TFT, in which a source electrode **11**, a drain electrode **12** and a base electrode **14** each made of chromium are formed on the surface of a glass substrate separate from each other. On the surfaces of the source electrode **11** and the drain electrode **12** there are formed n-type a-Si layers **31** and **32**, respectively, and on the surface of the base electrode **14** there is formed a p-type a-Si layer **33**. An intrinsic semiconductor layer (intrinsic a-Si layer) **30** is formed between the source and base electrodes, between the base and drain electrodes, and on the surfaces of the n-type a-Si layers **31** and **32**, as well as on the p-type a-Si layer **33**. A gate insulating film **20** made of a silicon nitride (SiN) film is formed on the surface of the intrinsic semiconductor layer **30**, and further a gate electrode **10** made of aluminum is formed on the gate insulating film **20**. Then, the whole structure of the device described above is encapsulated in a passivation film **22** made of a silicon nitride (SiN) film.

[0059] In the semiconductor device according to the second embodiment of the invention, the majority carriers are electrons and the minority carriers are holes the first embodiment of the invention.

[0060] According to this arrangement of the second embodiment of the invention, a positive voltage, which is positive relative to a voltage at the source electrode **11**, is applied to the base electrode **14**, which is in contact with p-type a-Si layer **33**, thereby causing the minority carrier of holes to be injected into the intrinsic semiconductor layer **30**. Thereby, under the same principle as described with reference to the first embodiment of the invention, it becomes possible to lower its threshold voltage and in consequence to improve its current drivability substantially.

[0061] In this second embodiment of the invention, the intrinsic semiconductor layer (intrinsic a-Si layer) **30** is

utilized as its active layer in the same manner as in the first embodiment of the invention, however, the invention is not limited thereto, since other semiconducting materials, such as, for example, polycrystalline silicon (poly-Si) or silicon germanium (SiGe) films, can be utilized as well to the same effect.

[0062] Third Embodiment:

[0063] **FIG. 6** is a cross-sectional view of a semiconductor device according to a third embodiment of the invention.

[0064] The semiconductor device according to the third embodiment of the invention has a structure of a planar-type TFT, in which a base electrode **14** made of chromium is formed on a glass substrate **1** in the center portion thereof, and n-type poly-Si layers **311** and **321** are formed on the glass substrate separated by base electrode **14** interposed therebetween. A p-type poly-Si layer **331** is formed on the surface of the base electrode **14**. Further, an intrinsic semiconductor layer (intrinsic poly-Si layer) **301** is formed surrounding both the base electrode **14** and the p-type poly-Si layer **331**. A gate insulating film **201** made of SiO<sub>2</sub> is formed on a part of the intrinsic semiconductor layer **301**, then, a gate electrode **10** made of aluminum is formed on the gate insulating film **201**. The n-type poly-Si layers **311** and **321** formed in contact in part with intrinsic semiconductor layer **301** are further connected with a source electrode **11** and a drain electrode **12** both made of chromium, respectively. Then, the source electrode **11**, the drain electrode **12** and the gate electrode **10** are surrounded by a protective insulating film **21**, and the entire structure of the device is encapsulated in a passivation film **22**. Also, in this third embodiment of the invention, the majority carriers are electrons and the minority carriers are holes as in the first embodiment of the invention.

[0065] According to this third embodiment of the invention, when a positive voltage, which is positive relative to a voltage at the source electrode **11**, is applied to the base electrode **14**, which is in contact with p-type poly-Si layer **331**, the minority carriers of holes are caused to be injected into the intrinsic semiconductor layer **301**. Thereby, under the same principle as operation of the semiconductor device indicated in **FIG. 1**, it becomes possible to lower the threshold voltage, thereby substantially improving the current drivability.

[0066] Further, according to this embodiment of the invention, the n-type poly-Si layers **311** and **321** are formed by means of self-alignment with respect to the pattern of the gate insulating film **201** and the gate electrode **10**. Namely, the pattern of the gate insulating film **201** and the gate electrode **10** is utilized as a mask to form the n-type poly-Si layers **311** and **321**. Thereby, a single step of photolithographic processing allows provision of both patterns of the n-type poly-Si layers **311** and **321**, as well as the gate electrode **10**, thereby simplifying the process of fabrication and reducing the cost of manufacture. Still further, there is another advantage that parasitic capacitances between the gate electrode **10** and the source electrode **11**, as well as between the gate electrode **10** and the drain electrode **12**, can be minimized since the width of overlapping of the gate electrode **10** with the n-type poly-Si layers **311**, **312** is minimized due to the self-alignment processing of the invention, thereby realizing a faster operation of the device.

[0067] Fourth Embodiment:

[0068] When a semiconductor device is formed having four terminals of a gate electrode, a source electrode, a drain electrode and a base electrode this semiconductor device having four terminals cannot be applied as it is to a transistor for use in a liquid crystal display or in its associated drive circuit, which principally requires three-terminal transistors. Therefore, in order to utilize this four-terminal transistor, an additional wiring must be provided for supplying a base current, which substantially complicates its circuit configuration and increases the area required for the circuits.

[0069] Thereby, with reference to FIG. 7, by taking into consideration the fact that an npn type bipolar transistor comprising an n-type a-Si layer 32, a p-type a-Si layer 33 and an n-type a-Si layer 31 is formed between the source electrode 11 and the channel ch in this field effect transistor (FET) of the fourth embodiment of the invention, it is contemplated that a base current can be supplied from the gate by providing a connection between the base electrode 14 and the gate electrode 10 via a resistance rb having an appropriate value.

[0070] When the gate and base are connected via resistance rb, the additional wiring that conventionally would have been required for supplying a base current to the base electrode can be eliminated, thereby simplifying the wiring substantially and improving the density of circuit integration, thereby allowing a finer resolution of display to be realized.

[0071] Fifth Embodiment:

[0072] FIG. 8 is a plan view of a planar type TFT forming a fifth embodiment of the invention, and FIG. 9 is a cross-sectional view of the planar type TFT taken along line X-X' in FIG. 8.

[0073] According to this embodiment of the invention, an intrinsic semiconductor layer 301 having a convex planar pattern and a pattern of a gate electrode 10 disposed in the center thereof are formed, and on the both sides thereof are formed n+layers 311 and 321 as the source and drain, respectively. By way of example, the n+layers 311 and 321 are formed on a glass substrate like the planar type transistor of FIG. 6. In the upper protruding portion of the intrinsic semiconductor layer 301 there is formed a p+layer 331, which serves as the base. The source electrode 11 and the drain electrode 12 are formed in contact with the n+layer 311 acting as a source and the n+layer 321 acting as a drain, respectively. A portion extending below the gate electrode from the intrinsic semiconductor layer 301 (channel) to the p+layer 331 is not doped with any impurities of P-type or N-type and forms a high resistance layer rb. The source and drain of the n+layers 311, 321, as well as the base of the p+layer 331, are separated by the intrinsic semiconductor layer 301 from each other.

[0074] Also, in this embodiment of the invention, like the first embodiment, the majority carrier is an electron and the minority carrier is a hole. By applying a positive voltage which is positive relative to the source electrode 11 to base electrode 14, which is in contact with the p-type poly-Si layer 331, the minority carrier of holes is caused to be injected into intrinsic poly-Si layer 301. Thereby, according to the same principle of operation as in the semiconductor element of FIG. 1, its threshold voltage can be decreased, thereby improving its current drive capability.

[0075] Further, by providing an electrical connection between base electrode 14 and gate electrode 10 according

to this embodiment of the invention, the operation available with the three terminal structure as indicated in FIG. 7 becomes possible. In this instance, since the high resistance layer rb acts to limit the base current, injection of an excessive base current is prevented, thereby allowing operation at a low power until the gate voltage increases to exceed, for example,  $\pm 5$  V.

[0076] Current-voltage characteristics of the TFTs according to this embodiment of the invention, such as drain current to gate voltage characteristics, as well as drain current to drain voltage characteristics, are compared to those of conventional TFTs in FIGS. 25A and 25B. It is clearly indicated in the drawings that TFTs of the invention have an improved current drive capability which is substantially greater than the conventional TFTs.

[0077] Sixth Embodiment:

[0078] With reference to FIG. 10, a plan view of a planar type TFT according to a sixth embodiment of the invention is illustrated. FIG. 11 is a cross-sectional view taken along line X-A in FIG. 10.

[0079] According to this embodiment of the invention, like the fifth embodiment, an intrinsic semiconductor layer 301 is formed to have a convex planar pattern, with a pattern of a gate electrode 10 disposed in the center thereof. On both sides of the intrinsic semiconductor layer 301 there are formed an n+layer 311 as the source and an n+layer 321 as the drain, respectively. Further, a p+layer 331 is formed as the base in a protruding portion of the convex patterned intrinsic semiconductor layer 301. Further, in a portion below the gate electrode extending from the intrinsic semiconductor layer 301 (channel) to the p+layer 331, there is formed a high electrical resistance layer rb which is not doped with any impurities of P-type or N-type. These features are the same as those in the fifth embodiment of the invention. Another feature of this embodiment is characterized by provision of an off-set layer roff made of the intrinsic semiconductor layer 301 between the n+layer 311 as the source and the n+layer 321 as the drain, and an intrinsic semiconductor layer 301 (channel) directly below the gate electrode 10. That is, the n+layers 311 operating as the source, the layer 321 operating as the drain, and the p+layer 331 operating as the base are arranged so that they are separated by intrinsic semiconductor layer 301 from each other. In order to realize such an arrangement, the pattern of the gate insulating film 20 is arranged to have a larger size than that of the gate electrode 10, and by utilizing the pattern of this gate insulating film 20 as a mask pattern for masking other counterparts, the n+layers 311, 321 operating as the source and drain or the p+layer 331 operating as the base are formed advantageously.

[0080] According to this embodiment of the invention, like the case of the first embodiment, the majority carrier is an electron and the minority carrier is a hole. In this arrangement, a positive voltage, which is positive relative to the source electrode 11, is applied to the base electrode 14, which is in contact with the p-type poly-Si layer 331, thereby causing the minority carrier of holes to be injected into the intrinsic poly-Si layer 301. Thereby, according to the same principle of operation as the semiconductor element of FIG. 1, the threshold voltage is successfully decreased,

thereby improving the current drive capability substantially. Further, by providing an electrical connection between the base electrode **14** and the gate electrode **10** according to this embodiment of the invention, the operation of the semiconductor element having a three-terminal configuration as indicated in **FIG. 7** can be realized. In this configuration, since the off-set layer **roff**, as well as the high resistance layer **rb**, acts to limit the base current, an excess base current injection is more effectively prevented, thereby ensuring operation at a low electric power until the gate voltage is increased substantially greater. Further, since the off-set layer acts to mitigate the electrical field present between the source electrode **11** and the drain electrode **12**, the occurrence of hot carriers is suppressed, thereby improving the reliability of the components substantially.

[0081] Seventh Embodiment:

[0082] **FIG. 12** is a schematic diagram of a circuit configuration of a complementary (CMOS) inverter using the semiconductor elements of **FIGS. 8 and 9**, and **FIG. 13** is a pattern configuration of the inverter circuit of **FIG. 12**. This type of inverter may be used, in particular, in the drive circuit in a liquid crystal display. The complementary inverter according to this embodiment of the invention is comprised of a P-type transistor PMOS and an N-type transistor NMOS, wherein each gate and base in each transistor are electrically connected via a base resistance **rb**. A first wiring electrode **105** coupling gate electrode **10** of the TFT with the input terminal **Vin** is provided extending to a protrusion of a TFT having a convex pattern, and is electrically connected via a second wiring electrode **106** to the base electrode formed in the protrusion.

[0083] Further, electrodes for supplying a reference voltage **Vss** and a power supply voltage **Vdd** to the circuit, as well as an output terminal **Vout**, are provided by the second wiring electrode **106**. In order to realize a fast circuit operation, the intrinsic poly-Si film **301**, which has a greater carrier mobility, is used as an active layer. Further, in order to prevent degradation of the characteristics during operation due to hot carriers, N-type transistors in which hot carriers tend to occur are fabricated to have the off-set layer **roff** as indicated in **FIG. 10**.

[0084] Transistors constituting the inverter circuit according to this embodiment are enabled to operate at a lower threshold voltage by the action described above. Thereby, operation at a lower supply voltage is enabled, advantageously decreasing power consumption in the circuit. Further, since the high resistance **rb** is inserted between the input terminal and the base electrode **14** of the TFT, an input current flowing from the input terminal to the source electrode via the base electrode **14** is suppressed, thereby decreasing power consumption.

[0085] Eighth Embodiment:

[0086] **FIG. 14** is a cross-sectional view of a complementary (CMOS) inverter circuit comprised of the inverted staggered TFTs indicated in **FIG. 1**, and **FIG. 15** shows the configuration of the inverter circuit of **FIG. 14**. The structure of an N-type transistor indicated to the left side in **FIG. 14** is the same as in **FIG. 1**. However, in order to realize a faster circuit operation, the intrinsic poly-Si film **301** having a greater carrier mobility is used as its active layer. The structure of a P-type transistor indicated to the right side in

**FIG. 14** has a complementary structure with respect to that of the above-mentioned N-type transistor. Namely, the n-type poly-Si layers **311**, **321** are formed selectively and partially on the surface of the intrinsic poly-Si film **301**, and further, the P-type poly-Si layers **331** are formed on the other areas of the surface of the intrinsic poly-Si film **301**, where the n-type poly-Si layers **311**, **321** are not formed. In the above P-type transistor, the minority carrier, which is electrons, is injected from the base electrode **14** and via the n-type poly Si layer **311**, whereby its threshold voltage is decreased by the same action as in the N-type transistor.

[0087] Therefore, it becomes possible for the inverter comprised of semiconductor elements according to the invention to be switched at a low input voltage **yin**, thereby effectively reducing power consumption in the circuit. Further, as in the embodiment of **FIG. 13**, the bases of the P-type transistor and N-type transistor are connected to their gate electrodes via a base resistance **rb**. Thereby, since an input current flowing from the input terminal to the source electrode through the base electrode **14** is suppressed, the power consumption can be substantially reduced.

[0088] Ninth Embodiment:

[0089] **FIG. 16** is a plan view of a unit picture element of a TFT active matrix constructed using the semiconductor elements of **FIG. 1**. A cross-section of the structure taken along line X-X' in **FIG. 16** is the same as that of **FIG. 1**. The unit picture element of the active matrix is comprised of a scanning electrode **100** formed on a glass substrate; a signal electrode **120** formed to intercross with the scanning electrode; a TFT formed in the vicinity of the intersection of these electrodes, including an intrinsic a-Si film **30**, a source electrode **11** and a base electrode **14** formed on the intrinsic a-Si film **30**; a pattern of an intrinsic a-Si film **30** formed separate from the intrinsic a-Si film **30** of the TFT and an n-type a Si film **31**; and a picture element electrode **13** connected to the source electrode **11** of the TFT.

[0090] As seen from **FIGS. 1 and 17**, the base electrode **14** is arranged to electrically contact the p-type a-Si layer **33** which is formed on the surface of the intrinsic a-Si film **30** which constitutes the TFT with a pattern of the n-type a-Si film **31**, which is formed on the surface of an intrinsic a-Si film **30** formed separate from the p-type a-Si layer **33**. A contact electrode **15** is formed separate from the base electrode **14** and in contact at its one end with the e-type a-Si film **31** on the intrinsic a-Si film **30**, and at the other end the contact electrode **15** is connected with scanning electrode **100** via a through-hole TH provided in a gate insulating film **20**.

[0091] In this arrangement, the pattern of the n-type a-Si film **31** formed on the intrinsic a-Si film **30**, which is in contact both with the base electrode **14** and the contact electrode **15**, provides for a base resistance corresponding to the base resistance **rb** in the equivalent circuit of **FIG. 7**. The value of resistance **rb** can be controlled by adjusting the gap between the base electrode **14** and the contact electrode **15**. Scanning electrode **100** can feed a base current since it is connected to base electrode **14** via the resistance, thereby eliminating the necessity of providing additional feeder wiring, and thereby preventing the aperture ratio of picture elements from decreasing. Further, since the base resistance is formed utilizing one of the semiconductor films which

constitute the TFT, an additional process for forming the resistance is eliminated, thereby simplifying the process of fabrication.

[0092] **FIG. 18** is a schematic diagram representing an equivalent circuit of a display constructed using the unit picture elements of **FIG. 16**. In the drawing of **FIG. 16**,  $X_iG$ ,  $X_{i+1}G$ , . . . , represent picture signal electrodes each connected to a picture element for forming a green filter G. Likewise,  $X_iB$ ,  $X_{i+1}B$ , . . . , represent picture signal electrodes each connected to a picture element for forming a blue filter, and  $X_iR$ ,  $X_{i+1}R$ , . . . , represent picture signal electrodes each connected to a picture element for forming a red filter.  $Y_i$ ,  $Y_{i+1}$ , . . . , are scanning electrodes **100** for selecting picture element columns  $X_1$ ,  $X_2$ , . . . , and these scanning electrodes **100** are connected to a vertical scanning circuit V. The picture signal electrodes are connected to a picture signal drive circuit H. A block SUP includes a power circuit for obtaining a plurality of stabilized power supplies by dividing a single power supply and a converter circuit for converting information suitable for display on a cathode ray tube supplied from a host computer to information suitable for display on a liquid crystal display. Each of a plurality of display regions surrounded by a plurality of scanning electrodes and a plurality of picture signal electrodes on the display area formed on the insulated substrate is comprised of a switching element connected to its associated scanning electrode and picture signal electrode, a picture element electrode connected to the switching element, a counterpoised electrode disposed opposite to the picture element electrode, and a liquid crystal layer interposed between the picture element electrode and the counterpoised electrode.

[0093] As this switching element provided in each display region, the semiconductor element of the invention is used.

[0094] By use of the semiconductor element of the invention as the switching element in each display region, an output voltage from vertical scanning circuit V can be decreased, thereby substantially reducing the power consumption in the liquid crystal display.

[0095] Tenth Embodiment:

[0096] **FIG. 19A** and **FIG. 19B** are plan views of a planar type TFTs according to a tenth embodiment of the invention. **FIGS. 19A and 19B** depict N-type and P-type TFTs, respectively. Further, **FIG. 19C** is a cross-sectional view taken along line Y-Y' in **FIG. 19A**, and **FIG. 19D** is a cross-sectional view taken along line X-X' in **FIG. 19A**. Other cross-sections along lines A-A', B-B' and Z-Z' of **FIGS. 19A and 19B** will be shown in **FIG. 24**, to be described later.

[0097] According to this embodiment of the invention, in the same manner as in the fifth embodiment of the invention, an intrinsic semiconductor layer **301** having a convex planar pattern is provided, and a pattern of a gate electrode **10** is disposed in the center thereof, and n+layers **311** and **321** are formed as the source and drain on both sides of the intrinsic semiconductor layer, respectively. Further, a p+layer **331** is formed as the base in the upper protrusion of the convex intrinsic semiconductor layer **301**. Further, as in the fifth embodiment of the invention, in a portion extending from the intrinsic semiconductor layer **301** (channel) under the gate electrode to p+layer **331**, there is formed a high resistance layer  $r_b$  which is not doped with any impurities of

P-type or N-type. According to this embodiment, an off-set layer  $r_{off}$  made of the intrinsic semiconductor layer **301** is formed between the n+layers **311**, **321** operating as the source and drain, and the intrinsic semiconductor layer (channel) immediately below the gate electrode **10**. Namely, the structures of the n+layers **311**, **321** operating as the source and drain and of the p+layer **331** operating as the base are separated by the intrinsic semiconductor layer **301**. In order to provide for such structures according to this embodiment, the pattern of the gate insulating film **20** is formed in a larger size than that of the gate electrode **10**, and then this pattern of the gate insulating film **20** is utilized as a mask for forming the n+layers **311**, **321** operating as the source and drain, or for forming the p+layer **331** operating as the base.

[0098] Further, as another feature according to this embodiment of the invention, as depicted in **FIGS. 19C and 19D**, gate electrode **10** has a structure such that it extends to the upper protruding portion of the convex type intrinsic semiconductor layer **301**, and it has a planar pattern having devoid portions above the p+layer **331** provided as the base and above the high resistance layer  $r_b$ , and further the p+layer **331** as the base and gate electrode **10** extending to the protruding portion are electrically connected by the base electrode **14**. By providing a connection between the p+layer **331** and the gate electrode **10**, the semiconductor device of this embodiment can be used as a three-terminal semiconductor element. By adoption of this planar circuit pattern in this embodiment of the invention, the gate electrode **10** and the base electrode **14** can be advantageously connected while minimizing an increase in area to be occupied by the semiconductor device. Further, by removing a part of the gate electrode **10** disposed on the high resistance layer  $r_b$ , changes in the values of the high resistance layer  $r_b$  due to a gate voltage can be eliminated, thereby providing a stabilized base current limiting function. Still further, since the off-set layer  $r_{off}$  in addition to the high resistance layer  $r_b$  acts to limit the base current, an excess base current injection can be more effectively prevented, thereby ensuring operation at a low power until the gate voltage is increased substantially. Furthermore, since the off-set layer acts to mitigate electrical field present between the source electrode **11** and the drain electrode **12**, generation of hot carriers is suppressed, thereby substantially improving the reliability of the semiconductor device.

[0099] **FIG. 20A** is a plan view of a unit picture element of a TFT active matrix constructed using the semiconductor device of **FIG. 19A**, and **FIG. 20B** is a cross-sectional view taken along line X-X' in **FIG. 20A**.

[0100] This active matrix is comprised of a scanning electrode **100** formed on the surface of a glass substrate; a signal electrode **120** formed so as to intercross with the scanning electrode; a TFT formed in the vicinity of the intersection of these electrodes, including an intrinsic poly-Si film **301**, a source electrode **11** and a base electrode **14**, each connected to the intrinsic poly-Si film **301** via a through-hole; and a picture element electrode **14** connected to the source electrode **11** of the TFT. As can be seen from **FIG. 20B** and as indicated in **FIG. 19C**, base electrode **14** connects the n+layer **331** and the gate electrode **10**. By connecting the base electrode **14** and the scanning electrode **100** in this manner according to the invention, the scanning electrode **100** is also adapted to feed a base current, hence

eliminating the necessity of providing additional feeder wiring, thereby preventing the aperture ratio of the picture element from being reduced. Still further, since the base resistance can be formed using a part of the semiconductor film which constitutes the TFT, an additional process for forming the resistance is eliminated, thereby simplifying the process of manufacture of the semiconductor device.

[0101] FIG. 21 shows an equivalent circuit of a display which is provided by integrating on the same substrate the drive circuits constructed using the CMOS inverter of FIGS. 12 and 13, and the TFT active matrix of FIG. 20A. This display is comprised of a TFT active matrix 50 according to the invention; a vertical scanning circuit 51 for driving the matrix; a horizontal scanning circuit 53 for dividing a video signal per scan into a plurality of blocks and supplying them in a time-sharing manner; data signal lines Vdr1, Vdg1, Vdb1, . . . , for supplying video signal data; and a switch matrix circuit 52 for supplying video signals, divided into a plurality of blocks, to the active matrix. Vertical scanning circuit 51 and horizontal scanning circuit 53 are constructed using a shift register and a buffer (to be described later with reference to FIG. 22), and are driven by clock signals CL1, CL2, and CKV. FIG. 22 depicts a scanning circuit corresponding to one scanning line. In FIG. 22, numeral 70 depicts a P-type transistor and 71 depicts an N-type transistor. Each of these transistors has a structure in which its base and gate are connected via resistance rb. The shift register operates at a timing using two phase clock signals (Vcp1, Vcp2) and inverse clock signals (Vcp1, Vcp2), reverses an input voltage and shifts it then to be transferred to the buffer. At the same time, this signal to be transferred to the buffer is also input as an input voltage to a shift register corresponding to the subsequent scanning line. The buffer outputs a pulse voltage at a maximum voltage of Vdd2, which becomes a scanning voltage for the active matrix display.

[0102] It has been confirmed that the shift register of a complementary type TFT using the semiconductor device according to the invention is able to operate at a half of the power consumption normally required with the conventional shift registers using conventional TFTs. Further, since TFTs for constituting the active matrix are constructed using the semiconductor device according to the invention, the output level or Vdd2 of the scanning circuit has been halved compared to the conventional level. Thereby, the total power consumption of the whole active matrix substrate has been reduced to one third of the conventional.

[0103] Although the planar type TFT was used in the above-mentioned embodiment of the invention, the invention is not limited thereto, since the inverted staggered type or staggered type TFTs as indicated in FIGS. 1 or 2 may be used as well. It should be noted, however, that since in the planar type semiconductor device the parasitic capacitance between the gate and source or drain can be reduced, a faster operation can be attained.

[0104] Eleventh Embodiment:

[0105] FIGS. 23A to 23D illustrate respective fabrication steps in cross-sectional view of the semiconductor device of the invention depicted in FIG. 1. A Cr film is accumulated by sputtering on the surface of a glass substrate 1 to a thickness of 100 nm and is patterned into a predetermined planar shape using a known photolithography process so as

to provide a gate electrode 10. Then, over the entire area of the substrate, including the surface of the gate electrode 10, there are formed a silicon nitride (SiN) film 20, an intrinsic amorphous silicon (a-Si) film 30, and an n-type a-Si film 31, sequentially using the plasma CVD method. The respective film thicknesses are 350 nm for the SiN film, 200 nm for the intrinsic a-Si film and 40 nm for the n-type a-Si film (see FIG. 23A).

[0106] After having patterned the intrinsic a-Si film and n-type a-Si film into predetermined planar shapes, a photo-resist PR having a predetermined planar shape is formed on an n-type a-Si film 31 such that by using the photo-resist as its mask, the n-type a-Si film 31 is patterned into a predetermined shape by plasma etching, that is, the n-type a-Si film 31 is separated into two parts including the n-type a-Si film 31 and the n-type a-Si film 32 (see FIG. 23B).

[0107] Subsequently, an ion beam IB which contains boron is irradiated over the entire area on the substrate with the photo-resist still remaining, thereby forming a p-type a-Si film 33 in an area on the surface of the intrinsic a-Si film 30 from which the n-type a-Si film 31 was removed partially (refer to FIG. 23C).

[0108] Then, after having removed the photo-resist PR, Cr and Al are sputtered to a thickness of 40 nm and 400 nm, respectively, and are each patterned into a predetermined shape so as to provide for a source electrode 11, drain electrode 12 and base electrode 14, respectively. Finally, a SiN film is formed by the plasma CVD method to a thickness of 400 nm as a passivation film 22, thus completing the fabrication of the semiconductor element of the invention (refer to FIG. 23D).

[0109] According to this embodiment of the invention, p-type a-Si layer 33 is formed by self-alignment with respect to the patterns of the n-type a-Si layers 31 and 32. That is, the p-type a-Si layer 33 is formed utilizing the patterns of the n-type a-Si layers 31, 32 as its own mask. Thereby, both the n-type a-Si layers 31, 32 and the p-type a-Si layer 33 can be formed advantageously by one photolithographic process according to the invention, thereby simplifying the process of fabrication and reducing the cost of manufacture.

[0110] Twelfth Embodiment:

[0111] With reference to FIGS. 24A to 24F, fabrication steps in the process of fabricating the complementary (CMOS) semiconductor device indicated in FIGS. 19A to 19D according to the invention are illustrated in respective cross-sectional views. In FIGS. 24A to 24F, sections indicated by A-A', Y-Y', B-B', Z-Z' correspond respectively to cross-sections indicated by A-A', Y-Y', B-B', Z-Z' in FIGS. 19A to 19D.

[0112] After forming an intrinsic a-Si film 30 on a glass substrate to a thickness of 50 nm by the LPCVD method, a high intensity XeCl excimer laser beam LASER is irradiated at an energy density of 330 mJ/cm<sup>2</sup> from the above such that the intrinsic a-Si film 30 is caused to melt and recrystallize to obtain an intrinsic polycrystalline silicon (poly-Si) film 301 (refer to FIG. 24A).

[0113] After patterning the poly-Si film 301 into a predetermined planar pattern, a SiO<sub>2</sub> film is formed to a thickness of 100 nm by the plasma CVD method, and an Al film is

formed to a thickness of 100 nm by the sputtering method, and they are patterned into respective planar patterns so as to provide a gate insulating film **20** and a gate electrode **10** (refer to **FIG. 24B**).

[**0114**] After forming a photo-resist pattern PR1 having a predetermined shape, and by using patterns of the photoresist PR1 and gate electrode **10** as its mask, an ion beam IP which contains phosphor is irradiated to form an n-type poly-Si layer **311** (refer to **FIG. 24C**).

[**0115**] After having removed the photo-resist pattern PR1, another photo-resist pattern PR2 is formed, and by using patterns of the photo-resist PR2 and gate electrode **10** as its mask, an ion beam which contains boron is irradiated thereover, thereby forming p-type poly-Si layers **331**. After having removed the photo-resist pattern PR2, an XeCl excimer laser beam is irradiated once again thereover at an energy density of 200 mJ/cm<sup>2</sup> so as to activate injected phosphor and boron, thereby decreasing the electrical resistance of the n-type poly-Si layer **311** and p-type poly-Si layer **321** (refer to **FIG. 24D**).

[**0116**] Then, an SiO<sub>2</sub> film is formed by the plasma CVD method to a thickness of 300 nm as a passivation film **22**, which is then patterned into a predetermined pattern, as depicted in **FIG. 24E**.

[**0117**] Finally, Cr and Al are deposited to a thicknesses of 40 nm and 400 nm, respectively, by sputtering, and then they are patterned into respective patterns to provide for a source electrode **11**, drain electrode **12** and base electrode **14**, thereby completing the process of fabrication of the semiconductor element of the invention, as indicated in **FIG. 24F**.

[**0118**] Thirteenth Embodiment:

[**0119**] **FIG. 26** is a diagram in cross-section of a liquid crystal display according to the invention. On a glass substrate **1** disposed below a liquid crystal layer **506** disposed in the center portion in **FIG. 26**, there are formed a scanning signal electrode **10** and a picture signal electrode **120** both intercrossing in the form of a matrix, a TFT which is formed in the vicinity of the intercrossing, and a picture element electrode **13** made of ITO which is driven via the TFT. On a counterposed glass substrate **508** disposed opposite to the glass substrate **1** with respect to the liquid crystal layer **506**, which is interposed therebetween, there are formed a counterposed electrode **510** made of ITO, a color filter **507**, a color filter protection film **511** and a shading film **512** which forms a shading black matrix pattern. The center portion of **FIG. 26** represents a cross-section of one picture element portion, the left side portion of the drawing represents the left side end portion in cross-section of a pair of glass substrates **1** and **508** wherein an external lead terminal is provided, and the right side portion of the drawing represents the right side end portion in cross-section of the pair of glass substrates **1** and **508** wherein no external lead terminal is provided.

[**0120**] Seal material SL, provided on both sides of the left end portion and the right end portion, is formed so as to seal the liquid crystal layer **506**, and is formed along the whole portion of the periphery of the pair of glass substrates **1** and **508** except for a liquid crystal injection port (not shown). The seal material may be made of epoxy resin, for example. Counterposed electrode **510** provided on the counterposed

glass substrate **508** is connected at least at a part thereof to the external lead wiring on the glass substrate **1** via silver paste SIL. This external connection wiring is formed in the same fabrication process as employed for the scanning signal wiring **10**, source electrode **11**, picture signal wiring **120** and base electrode **14**. Respective layers of orientation film ORI1, ORI2, picture element electrode **13**, protection film **22**, and gate SiN film **20** are formed inside the seal material SL. Polarization plate **505** is formed on each outer surface of the pair of glass substrates **1** and **508**.

[**0121**] A liquid crystal layer **506** is interposed between the upper orientation film ORI1 and the bottom orientation film ORI2 which set the orientation of the liquid crystal molecules, and the liquid crystal is sealed by the seal material SL. The bottom orientation film ORI1 is formed in the upper portion of protection film **20** on the glass substrate **1**. On the internal surface of the counterposed glass substrate **508**, there are formed sequentially by lamination shading film **512**, color filter **507**, color filter protection film **511**, counterposed electrode **510** and the upper orientation film ORI2. This liquid crystal display is constructed by the steps of separately forming the layers on the glass substrate **1** and the layers on the counterposed glass substrate **508**; laminating the glass substrate **1** and the counterposed glass substrate **508**; and sealing the liquid crystal **506** in a space therebetween. Then, a TFT driven color liquid crystal display is provided by effecting adjustment of the transparency of light from a backlight BL using picture element electrode **13**.

[**0122**] Since the semiconductor device according to the invention described above is used as a TFT to drive the picture element electrode **13** at a reduced voltage, liquid crystal displays capable of operating at a reduced power consumption have been realized.

[**0123**] Fourteenth Embodiment:

[**0124**] **FIG. 27** is a diagram in cross-section of a reflection type liquid crystal display according to the invention. Only a cross-section of a picture element portion is indicated. On a glass substrate **1** provided below a liquid crystal layer **506**, which is in the center portion in **FIG. 27**, there are formed a scanning signal electrode **10** and a picture signal electrode **120** intersecting each other in the form of a matrix, and a TFT is formed in the vicinity of the intersection for driving a picture element electrode **130** provided thereon. According to this embodiment of the invention, the picture element electrode **130** is made of Al. On the internal surface of counterposed glass substrate **508** disposed opposite to the glass substrate **1** via the liquid crystal layer **506**, there are formed counterposed electrode **510**, color filter **507**, color filter protection film **511**, and a shading film **512**, which forms a shading black matrix pattern. Further, a phase plate **530** for shifting the phase of the light and a polarization plate **505** are formed on the outer surface of counterposed glass substrates **1**, **508**. Respective layers of orientation films ORI1 and ORI2, a picture element electrode **13**, a protection film **22**, and a gate SiN film **20** are formed inside a seal material (not shown). The liquid crystal layer **506** is inserted between the upper and the bottom orientation films ORI1 and ORI2, which set the orientation of the liquid crystal molecules, and the liquid crystal is sealed by the seal material. The bottom orientation film ORI1 is formed in the upper portion of the protection film **22** on the glass substrate **1**. On the internal surface of counterposed glass substrate

**508**, there are formed in lamination sequentially a shading film **512**, a color filter **507**, a color filter protection film **511**, a counterposed electrode **510** and the upper orientation film ORI2. This liquid crystal display of the invention is fabricated by the steps of separately forming layers on the glass substrate **1** and on the counterposed substrate **508**; then, laminating both the glass substrate **1** and the counterposed substrate **508**; and sealing the liquid crystal **506** in a space therebetween.

[0125] Since this embodiment of the invention is of a reflection type display, incident light comes from a light source provided outside the counterposed glass substrate **508**, and this incident light is reflected from a mirror-finished surface of the picture element electrode **130**. A TFT driven reflection type color liquid crystal display according to the invention is thus provided in which the intensity of the reflected light is adjusted in the portion of liquid crystal layer **506**. In this type of reflection type display, since the back-light which consumes considerable electric power is eliminated, a low power consuming liquid crystal display can be realized. Further, if the above-mentioned semiconductor device of the invention is utilized as TFTs for driving the picture element electrode **130** and/or TFTs for constituting associated peripheral drive circuits, since the electric power consumed in the active matrix substrate components can be reduced, there can be realized a very low power consuming liquid crystal display. This type of liquid crystal display of the invention is most preferable for use as an image display device in a portable information terminal which is driven by dry cells.

[0126] As described heretofore, there is an advantage according to the invention in that the field effect semiconductor device of the invention can reduce its threshold voltage substantially, thereby decreasing the operating voltage of its circuit or active matrix, and thereby reducing the power consumption in the display.

What is claimed is

1. A liquid crystal display having a pair of substrates at least one of which is transparent and a liquid crystal layer held between said pair of substrates, wherein

on one of said pair of substrates there are formed a plurality of semiconductor elements disposed in a matrix; wherein

each of said plurality of semiconductor elements comprises: a first, a second, a third and a fourth electrodes; a pair of a first conducting type semiconductor layers separate from each other and connected to said second and said third electrodes, respectively; an intrinsic semiconductor layer provided in contact with both the pair of the first conducting type semiconductor layers; and a second conducting type semiconductor layer formed on the intrinsic semiconductor layer, and wherein

said first electrode is formed on said intrinsic semiconductor layer via an insulating film, and

said fourth electrode is formed on the second conducting semiconductor layer which is formed on said intrinsic semiconductor layer.

2. A liquid crystal display according to claim 1, wherein said pair of the first conducting type semiconductor layers

and said second conducting type semiconductor layer are separated from each other by said intrinsic semiconductor layer.

3. A liquid crystal display according to claim 2, wherein the intrinsic semiconductor layer has a region extending greater than a region of the insulating layer toward said pair of the first conducting type semiconductor layers on said substrate.

4. A liquid crystal display according to claim 1, wherein said first electrode and said fourth electrode are electrically connected via a resistance.

5. A liquid crystal display according to claim 1, wherein said intrinsic semiconductor layer, said first conducting type semiconductor layers, and said second conducting type semiconductor layer are comprised of a semiconductor film made of either one of silicon, silicon germanium and silicon carbide.

6. A liquid crystal display according to claim 1 wherein said intrinsic semiconductor layer, said pair of the first conducting type semiconductor layers, and the second conducting type semiconductor layer are made of a polycrystalline silicon film, respectively.

7. A liquid crystal display according to claim 1, wherein said plurality of the first conducting type layers and said second conducting type semiconductor layer are an N-type semiconductor and a P-type semiconductor, respectively.

8. A liquid crystal display according to claim 1, wherein said intrinsic semiconductor layer is injected with a current carrier from the fourth electrode via the second conducting type semiconductor layer.

9. A liquid crystal display according to claim 1, wherein said first, said second, said third and said fourth electrodes correspond to a gate, a source, a drain and a base electrodes, respectively.

10. A liquid crystal display according to claim 1, wherein each of said plurality of semiconductor elements has a structure either of a planar type, an inverted staggered type or a normal staggered type.

11. A liquid crystal display according to claim 10 wherein said first electrode is formed on one of said pair of substrates, said insulating layer is formed on said first electrode, said intrinsic semiconductor layer is formed on said insulating layer, and said pair of the first conducting type semiconductor layers are formed on said intrinsic semiconductor layer.

12. A liquid crystal display according to claim 10 wherein said second electrode, said third electrode and said fourth electrode are formed on one of said pair of substrates.

13. A liquid crystal display having a pair of substrates at least one of which is transparent, and a liquid crystal layer which is held between said pair of substrates, wherein

one of said pair of substrates has a display region and a drive circuit region for driving said display region disposed on the surface thereof, wherein

in said drive circuit region, there are formed a plurality of complementary N-type and P-type semiconductor elements which constitute a shift register, wherein

each one of said N-type semiconductor elements formed in said drive circuit region comprises: a first, a second, a third and a fourth electrodes; a pair of N-type conducting semiconductor layers separated from each other and connected to said second and the third electrodes, respectively; an intrinsic semiconductor

layer connected to said pair of N-type conducting semiconductor layers; and a P-type conducting semiconductor layer which is formed partially on said intrinsic semiconductor layer, wherein said first electrode is formed on said intrinsic semiconductor layer via an insulating film, and said fourth electrode is formed on the P-type conducting semiconductor layer which is formed partially on said intrinsic semiconductor layer, and

each of said plurality of P-type conducting semiconductor layers formed in said drive circuit region comprises: a first, a second, a third and a fourth electrodes; a pair of P-type conducting semiconductor layers which are formed separate from each other and connected to said second and said third electrodes, respectively; an intrinsic semiconductor layer connected to said pair of P-type conducting semiconductor layers; and an N-type conducting semiconductor layer formed on the intrinsic semiconductor layer, and wherein said first electrode is formed on said intrinsic semiconductor layer via an insulating film, and said fourth electrode is formed on the N-type conducting semiconductor layer which is formed on said intrinsic semiconductor layer.

**14.** A liquid crystal display according to claim 13, wherein said semiconductor element formed in said display region is an N-type semiconductor element.

**15.** A liquid crystal display according to claim 14, wherein said N-type semiconductor element formed in said display region comprises: a first, a second, a third and a fourth electrodes; a pair of N-type conducting semiconductor elements formed separate from each other and connected to said second and said third electrodes, respectively; an intrinsic semiconductor layer connected to said pair of N-type conducting semiconductor layers; and a P-type conducting semiconductor layer formed on the intrinsic semiconductor layer, wherein said first electrode is formed on said intrinsic semiconductor layer via an insulating film, and said fourth electrode is formed on the P-type conducting semiconductor layer which is formed said intrinsic semiconductor layer.

**16.** A liquid crystal display according to claim 13, wherein the semiconductor elements formed in said display region and said drive circuit region are either of a planar type, inverted staggered type and normally staggered type.

**17.** A liquid crystal display according to claim 13, wherein the intrinsic semiconductor layer, N-type conducting semiconductor layer and P-type conducting semiconductor layer are made of a polycrystalline silicon film, respectively.

**18.** A liquid crystal display according to claim 13, wherein said pair of N-type conducting semiconductor layers and said P-type conducting semiconductor layer are separated from each other by said intrinsic semiconductor layer.

**19.** A liquid crystal display according to claim 18, wherein a region of said intrinsic semiconductor layer in a vertical direction of said substrate extends more than a region of said insulating layer at least toward said pair of N-type conducting semiconductor layers.

**20.** A liquid crystal display according to claim 13, wherein said first and said fourth electrodes are electrically connected via an electric resistance.

**21.** A liquid crystal display having a pair of substrates at least one of which is transparent, and a liquid crystal layer which is held between said pair of substrates, wherein

one of said pair of substrates has a display region and a drive circuit region for driving said display region disposed on the surface thereof, wherein

said display region has: a plurality of scanning signal electrodes and a plurality of picture signal electrodes intercrossing with said plurality of scanning electrodes in a matrix; a plurality of N-type semiconductor elements formed at crosspoints corresponding to intersections between said plurality of scanning signal electrodes and said plurality of picture signal electrodes; and a plurality of picture element electrodes connected to said semiconductor elements respectively, and

said drive circuit region has a plurality of complementary N-type and P-type semiconductor elements formed thereon, which constitute a vertical scanning circuit and a picture signal drive circuit, wherein,

said N-type semiconductor element formed in said display region or in said drive circuit region comprises: a first, a second, a third and a fourth electrodes; N-type conducting semiconductor layers connected to said second and said third electrodes, respectively; an intrinsic semiconductor layer connected to these N-type conducting semiconductor layers; and a P-type conducting semiconductor layer formed on the intrinsic semiconductor layer, wherein said first electrode is formed on the intrinsic semiconductor layer via an insulating film, and said fourth electrode is formed on the surface of the P-type semiconductor layer which is formed on said intrinsic semiconductor layer, and

said P-type semiconductor element formed in said drive circuit region comprises: a first, a second, a third and a fourth electrodes; P-type conducting semiconductor layers connected to said second and said third electrodes, respectively; an intrinsic semiconductor element connected to these P-type conducting semiconductor layers; and an N-type semiconductor element formed on the intrinsic semiconductor layer, wherein said first electrode is formed on the intrinsic semiconductor element via an insulating film, and said fourth electrode is formed on the N-type conducting semiconductor layer which is formed on the intrinsic semiconductor element, and wherein

said first electrode is connected to said scanning signal electrode, said second electrode is connected to said picture signal electrode, and said fourth electrode is connected to said first electrode via an electric resistance.

**22.** A liquid crystal display according to claim 21, wherein said pair of N-type conducting semiconductor elements and said P-type conducting semiconductor element are separated from each other by said intrinsic semiconductor layer.

**23.** A liquid crystal display according to claim 22, wherein said intrinsic semiconductor layer has a region extending further than a region of said insulating layer toward said pair of N-type conducting semiconductor layers on said substrate.

\* \* \* \* \*

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#### 摘要(译)

适用于液晶显示器的显示区域或用于驱动显示区域的驱动电路区域的半导体元件包括第一，第二，第三和第四电极；一对第一导电型半导体层，彼此分开并分别连接到第二和第三电极；与该对第一导电型半导体层连接的本征半导体层；形成在本征半导体层上的第二导电类型半导体层，其中绝缘膜插入在第一电极和本征半导体层之间，第四电极形成在形成在本征半导体层上的第二导电类型半导体层上。

